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DISPLAY DEVICE

Abstract

A display device includes a base layer, a circuit layer on the base layer, and an element layer on the circuit layer and including light emitting elements and light receiving elements. The circuit layer includes pixel driving circuits connected to the light emitting elements, sensor driving circuits connected to the light receiving elements, gate wirings connected to the pixel driving circuits, first readout lines connected to a first group of sensor driving circuits among the sensor driving circuits, second readout lines connected to a second group of sensor driving circuits among the sensor driving circuits, connecting lines electrically connected with the second readout lines, respectively, in the display area, and a shielding pattern between the gate wirings and the connecting lines.

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Background/Summary

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application claims priority under 35 U.S.C. § 119 to Korean Patent Application No. 10-2024-0022396 filed on Feb. 16, 2024, in the Korean Intellectual Property Office, the disclosure of which is incorporated by reference herein in its entireties.

BACKGROUND

[0002] Embodiments described herein relate to a display device in which the size of a non-display area is reduced.

[0003] A display device may provide functions that enable a user to interact with the display device. For example, a display device may display an image to provide information to the user and may sense a user input such as a user's touch or biometric information. To sense or recognize biometric information, a display device may use a capacitive sensing technique for sensing a change in capacitance between electrodes in the display device, a light sensing technique for sensing incident light using an optical sensor, or an ultrasonic sensing technique for sensing vibration using a piezoelectric element.

SUMMARY

[0004] Embodiments of the present disclosure provide a display device that has a biometric information recognition function and in which the area of a non-display area is relatively small, e.g., reduced when compared to some prior display devices.

[0005] According to an embodiment, a display device having a display area and a non-display area includes a base layer, a circuit layer on the base layer, and an element layer that is on the circuit layer and that includes light emitting elements and light receiving elements in the display area.

[0006] The circuit layer includes pixel driving circuits connected to the light emitting elements, sensor driving circuits connected to the light receiving elements, data lines connected to the pixel driving circuits, gate wirings connected to the pixel driving circuits, first readout lines connected to a first group of sensor driving circuits among the sensor driving circuits, second readout lines spaced apart from the first readout lines in a first direction and connected to a second group of sensor driving circuits among the sensor driving circuits, connecting lines electrically connected with the second readout lines, respectively, in the display area, and a shielding pattern that overlaps the gate wirings and the connecting lines when viewed from above a plane and that is disposed between the gate wirings and the connecting lines in a normal direction perpendicular to the plane.

[0007] According to an embodiment, an electronic device having a display area and a non-display area includes a base layer, a circuit layer on the base layer, and an element layer that is on the circuit layer and that includes light emitting elements and light receiving elements disposed to correspond to the display area.

[0008] The circuit layer includes pixel driving circuits connected to the light emitting elements, sensor driving circuits connected to the light receiving elements, data lines connected to the pixel driving circuits, gate wirings connected to the pixel driving circuits, voltage lines connected to the pixel driving circuits, first readout lines connected to a first group of sensor driving circuits among the sensor driving circuits, second readout lines spaced apart from the first readout lines in a first direction and connected to a second group of sensor driving circuits among the sensor driving circuits, vertical connecting lines that are electrically connected with the second readout lines, respectively, in the display area and that cross the gate wirings, and a shielding pattern that overlaps the gate wirings and the vertical connecting lines. The shielding pattern extends from at least one of the voltage lines and is between the gate wirings and the vertical connecting lines in a normal direction perpendicular to the plane.

Description

BRIEF DESCRIPTION OF THE FIGURES

[0009] The above and other objects and features of the present disclosure will become apparent by describing in detail embodiments thereof with reference to the accompanying drawings.

[0010] FIG. **1** is a perspective view of a display device according to an embodiment of the present disclosure.

[0011] FIG. **2**A is an exploded perspective view of the display device according to an embodiment of the present disclosure.

[0012] FIG. **2**B is a sectional view of the display device according to an embodiment of the present disclosure.

[0013] FIG. **3** is a block diagram of the display device according to an embodiment of the present disclosure.

[0014] FIG. **4**A is a circuit diagram illustrating a pixel and a sensor according to an embodiment of the present disclosure.

[0015] FIG. **4**B is a waveform diagram illustrating operations of the pixel and the sensor illustrated in FIG. **4**A.

[0016] FIG. **5**A is a plan view of a display panel according to an embodiment of the present disclosure.

[0017] FIG. **5**B is an enlarged view of a portion of the display panel illustrated in FIG. **5**A.

[0018] FIG. **6** is a sectional view of a display panel according to an embodiment of the present disclosure.

[0019] FIG. **7**A is a plan view illustrating a portion of a display panel according to an embodiment of the present disclosure.

[0020] FIG. **7**B is an enlarged view of portion BB of the display panel illustrated in FIG. **7**A.

[0021] FIG. **7**C is a sectional view taken along line I-I′ illustrated in FIG. **7**B.

[0022] FIG. **8**A is a plan view illustrating a portion of a display panel according to an embodiment of the present disclosure.

[0023] FIG. **8**B is an enlarged view of portion CC of the display panel illustrated in FIG. **8**A.

[0024] FIG. **8**C is a sectional view taken along line II-II′ illustrated in FIG. **8**B.

[0025] FIGS. **9**A. **9**B, **9**C, **9**D, **9**E, **9**F, **9**G, and **9**H are plan views illustrating an arrangement of patterned circuit layers in a display panel according to an embodiment of the present disclosure.

[0026] FIG. **10**A is a plan view illustrating a portion of a display panel according to an embodiment of the present disclosure.

[0027] FIG. **10**B is an enlarged view of portion EE of the display panel illustrated in FIG. **10**A.

[0028] FIG. **11**A is a plan view illustrating a portion of a display panel according to an embodiment of the present disclosure.

[0029] FIG. **11**B is an enlarged view of portion FF of the display panel illustrated in FIG. **11**A.

[0030] FIGS. **12**A and **12**B are sectional views illustrating light emitting elements and light receiving elements in a display panel according to an embodiment of the present disclosure.

DETAILED DESCRIPTION

[0031] In this specification, a component (or, an area, a layer, a part, etc.) referred to as being “on”, “connected to” or “coupled to” another component means that the component may be directly on, connected to, or coupled to the other component or a third component may be present therebetween.

[0032] Identical reference numerals in different drawings refer to similar or identical components. Additionally, in the drawings, the thicknesses, proportions, and dimensions of components may be exaggerated for ease of illustration or description.

[0033] Terms such as first, second, and the like may be used to describe various components, but

the components should not be limited by these terms. The terms may be used only for distinguishing one component from other components. For example, without departing the scope of the present disclosure, a first component may instead be referred to as a second component, and similarly, the second component may instead be referred to as the first component. The terms of a singular form may include plural forms unless otherwise specified. As used herein, the term "and/or" includes all combinations of one or more of the related components.

[0034] Terms such as "below", "under", "above", and "over" are used herein to describe a relationship of components illustrated in the drawings. The terms are relative concepts and may be described based on directions illustrated in the drawing.

[0035] Terms such as "comprise", "include", and "have", when used herein, specify the presence of stated features, numbers, steps, operations, components, parts, or combinations thereof, but do not preclude the presence or addition of one or more other features, numbers, steps, operations, components, parts, or combinations thereof.

[0036] Unless otherwise defined, all terms used herein, including technical or scientific terms, have the same meanings as those generally understood by those skilled in the art to which the present disclosure pertains. Such terms as those defined in a generally used dictionary are to be interpreted as having meanings corresponding to the contextual meanings in the relevant field of art, and terms used herein are not to be interpreted as having ideal or excessively formal meanings unless clearly defined as having such in the present disclosure.

[0037] Hereinafter, embodiments of the present disclosure will be described with reference to the accompanying drawings.

[0038] FIG. **1** is a perspective view of a display device according to an embodiment of the present disclosure. FIG. **2**A is an exploded perspective view of the display device according to an embodiment of FIG. **1**. FIG. **2**B is a sectional view of the display device according to an embodiment of FIG. **1**.

[0039] Referring to FIGS. **1**, **2**A, and **2**B, a display device DD according to an embodiment of the present disclosure may have a rectangular shape with short sides parallel to a first direction DR**1** and long sides parallel to a second direction DR**2** crossing the first direction DR**1**. However, without being limited thereto, the display device DD may have various shapes such as a circular shape, a polygonal shape, and the like.

[0040] The display device DD may be a device activated electrically. The display device DD may include various embodiments and may be used in various applications. For example, the display device DD may be applied to or in an electronic device such as a smart watch, a tablet computer, a notebook computer, a computer, a smart television, and the like. The display device DD may be referred to as the electronic device.

[0041] A third direction DR**3** is a normal direction substantially perpendicular to a plane defined by the first direction DR**1** and the second direction DR**2**. The expression "when viewed from above the plane" used herein may mean when viewed with a line of sight along the third direction DR**3**.

[0042] The upper surface of the display device DD may be defined as a display surface IS and may be parallel to the plane defined by the first direction DR**1** and the second direction DR**2**. Images IM generated by the display device DD may be provided to a user through the display surface IS.

[0043] The display surface IS may be divided into a transmissive area TA and a bezel area BZA. The transmissive area TA may be an area on which the images IM are displayed. The user may visually recognize the images IM through the transmissive area TA. In this embodiment, the transmissive area TA is illustrated in a rounded quadrangular shape. However, this is illustrative, and the transmissive area TA may have various shapes and is not limited to the illustrated embodiments.

[0044] The bezel area BZA is adjacent to the transmissive area TA. The bezel area BZA may have a fixed color, e.g., black. The bezel area BZA may surround the transmissive area TA. Accordingly, the bezel area BZA may define the shape or boundaries of the transmissive area TA. However, this

example is illustrative, and the bezel area BZA may be adjacent to only one side of the transmissive area TA or may be omitted.

[0045] The display device DD may sense an external input applied to the display device DD from outside the display device DD. The external input may be of various types. For example, the external input may be a part of the user's body (e.g., a hand US_F of the user) or a separate device (e.g., an active pen or a digitizer) contacting the display device DD. The external input is not limited to contact but may correspond to other actions (e.g., hovering) that is applied in proximity to the display device DD or applied adjacent to the display device DD at a certain distance. In addition, the external input may have various forms such as force, pressure, temperature, light, and the like.

[0046] The display device DD may sense a user's biometric information. A biometric information sensing area capable of sensing the user's biometric information may be provided on the display surface IS of the display device DD. The biometric information sensing area may cover all of the transmissive area TA or may only be in a portion of the transmissive area TA. FIG. **1** illustrates an example that uses the entire transmissive area TA as a biometric information sensing area.

[0047] The display device DD may include a window WM, a display module DM, and a housing EDC. In this embodiment, the window WM and the housing EDC are coupled to each other to form the exterior of the display device DD.

[0048] The front surface of the window WM defines the display surface IS of the display device DD. The window WM may include an optically clear insulating material. For example, the window WM may include glass or plastic. The window WM may have a multi-layer structure or a single-layer structure. For example, the window WM may include a stack of plastic films attached together using an adhesive or may include a glass substrate and a plastic film coupled to each other using an adhesive.

[0049] The display module DM may include a display panel DP and an input sensing layer ISL. The display panel DP may display an image that depends on an electrical signal, and the input sensing layer ISL may sense an external input applied from outside the display device DD. The external input may take various forms such as described above.

[0050] The display panel DP according to an embodiment of the present disclosure may be an emissive display panel, but embodiments are not limited thereto. In some embodiments, the display panel DP may be an organic light emitting display panel, an inorganic light emitting display panel, or a quantum-dot light emitting display panel. An emissive layer of an organic light emitting display panel may include an organic luminescent material, and an emissive layer of an inorganic light emitting display panel may include an inorganic luminescent material. An emissive layer of a quantum-dot light emitting display panel may include quantum dots and quantum rods. Hereinafter, an embodiment in which the display panel DP is an organic light emitting display panel is described as an example.

[0051] Referring to FIG. **2**B, the display panel DP may include a base layer BL, a circuit layer DP_CL, an element layer DP_ED, and an encapsulation layer TFE. The display panel DP may be a flexible display panel. However, the present disclosure is not limited thereto. For example, the display panel DP may be a foldable display panel that is folded about a folding axis, or the display panel DP may be a rigid display panel.

[0052] The base layer BL may include a synthetic resin layer. The synthetic resin layer may be a polyimide-based resin layer, and the material thereof is not particularly limited. In addition, the base layer BL may include a glass substrate, a metal substrate, or an organic/inorganic composite substrate.

[0053] The circuit layer DP_CL is on the base layer BL and is between the base layer BL and the element layer DP_ED. The circuit layer DP_CL may include at least one insulating layer and a circuit element. Hereinafter, the insulating layer included in the circuit layer DP_CL is referred to as an intermediate insulating layer. The intermediate insulating layer may include at least one

intermediate inorganic film and at least one intermediate organic film. The circuit element may include a plurality of pixel driving circuits, one for each of a plurality of pixels used for displaying an image and a plurality of sensor driving circuits, one for each of a plurality of sensors used for recognizing external information. The external information may be biometric information. In an embodiment of the present disclosure, the sensor may be a fingerprint recognition sensor, a proximity sensor, an iris recognition sensor, a blood pressure measurement sensor, an illuminance sensor, or the like. Alternatively, the sensor may be an optical sensor for optically recognizing biometric information. The circuit layer DP_CL may further include signal lines connected to the pixel driving circuits and/or the sensor driving circuits.

[0054] The element layer DP_ED may include light emitting elements in the pixels and light receiving elements in the sensors. In an embodiment of the present disclosure, each light receiving element may be or include a photo diode. In one example, the light receiving element may be a sensor that senses, or reacts to, light reflected by a fingerprint of the user. Embodiments of the circuit layer DP_CL and the element layer DP_ED are described further below with reference to FIGS. **6** to **12**B.

[0055] The encapsulation layer TFE seals and protects the element layer DP_ED. The encapsulation layer TFE may include at least one organic film and at least one inorganic film. The inorganic film may include an inorganic material and may protect the element layer DP_ED from moisture/oxygen. The inorganic film may include a silicon nitride layer, a silicon oxy nitride layer, a silicon oxide layer, a titanium oxide layer, or an aluminum oxide layer, but is not particularly limited thereto. The organic film may include an organic material and may protect the element layer DP_ED from foreign matter such as dust particles.

[0056] The input sensing layer ISL may be formed on the display panel DP. The input sensing layer ISL may be directly on the encapsulation layer TFE. According to an embodiment of the present disclosure, a continuous process may form at least one upper layer of the display panel DP and then the input sensing layer ISL. That is, when the input sensing layer ISL is directly on the display panel DP, an adhesive film is not between the input sensing layer ISL and the encapsulation layer TFE. Alternatively, an adhesive film may be disposed between the input sensing layer ISL and the display panel DP. In this case, the input sensing layer ISL may not be manufactured together with the display panel DP by a continuous process and may be manufactured separately from the display panel DP and then fixed to the upper surface of the display panel DP using the adhesive film.

[0057] The input sensing layer ISL may sense an external input (e.g., a touch of the user), may generate a certain input signal that depends on the external input, and may provide the input signal to the display panel DP. The input sensing layer ISL may include a plurality of sensing electrodes for sensing the external input. The sensing electrodes may sense the external input using a capacitive type sensing process. The display panel DP may receive the input signal from the input sensing layer ISL and may generate an image corresponding to the input signal.

[0058] The display module DM may further include a color filter layer CFL. In an embodiment of the present disclosure, the color filter layer CFL may be on the input sensing layer ISL. However, the present disclosure is not limited thereto. The color filter layer CFL may be between the display panel DP and the input sensing layer ISL. The color filter layer CFL may include a plurality of color filters and a black matrix.

[0059] The structures of the input sensing layer ISL and the color filter layer CFL are described further below.

[0060] The display device DD according to an embodiment of the present disclosure may further include an adhesive layer AL. The adhesive layer AL may attach the window WM to the input sensing layer ISL. The adhesive layer AL may include an optically clear adhesive, an optically clear adhesive resin, or a pressure sensitive adhesive (PSA).

[0061] The display module DM may further include a driver chip DIC and sensor chips SIC**1** and SIC**2** as shown in FIG. **2**A. In an embodiment of the present disclosure, the driver chip DIC and the

sensor chips SIC**1** and SIC**2** may be mounted on the display panel DP. The driver chip DIC and the sensor chips SIC**1** and SIC**2** may be adjacent to one end portion (hereinafter, referred to as the first end portion) of the display panel DP. Although FIG. **2**A illustrates an example in which the driver chip DIC and the sensor chips SIC**1** and SIC**2** are adjacent to the first end portion of the display panel DP, the present disclosure is not limited thereto. For example, the driver chip DIC may be disposed adjacent to the first end portion of the display panel DP, and the sensor chips SIC**1** and SIC**2** may be disposed adjacent to a second end portion of the display panel DP that faces away from the first end portion.

[0062] In an embodiment of the present disclosure, the sensor chips SIC**1** and SIC**2** may include the first sensor chip SIC**1** on one side (hereinafter, referred to as the first side) of the driver chip DIC and the second sensor chip SIC**2** on a second side of the driver chip DIC that is different from the first side. Alternatively, the first and second sensor chips SIC**1** and SIC**2** may be integrated into one sensor chip, and the one sensor chip may be adjacent to the driver chip DIC. In the present disclosure, the number of sensor chips SIC**1** and SIC**2** and the number of driver chips DIC are not particularly limited.

[0063] The housing EDC may be coupled to the window WM. The housing EDC with the window WM provide an inner space of the display device DD. The display module DM may be accommodated in the inner space. The housing EDC may include a material having a relatively high rigidity. For example, the housing EDC may include glass, plastic, or metal, or may include a plurality of frames and/or plates formed of a combination thereof. The housing EDC may stably protect components in the inner space of the display device DD from external impact. Although not illustrated, a battery module for supplying power required for overall operation of the display device DD may be disposed between the display module DM and the housing EDC.

[0064] FIG. **3** is a block diagram of the display device according to an embodiment of the present disclosure.

[0065] Referring to FIG. **3**, the display device DD includes the display panel DP, a panel driver, and a driving controller **100**. In an embodiment of the present disclosure, the panel driver includes a data driver **200**, a scan driver **300**, an emission driver **350**, a voltage generator **400**, and a readout circuit **500**.

[0066] The driving controller **100** receives an image signal RGB and a control signal CTRL. The driving controller **100** generates image data DATA by converting the data format of the image signal RGB according to the specification of an interface with the data driver **200**. The driving controller **100** outputs a first control signal SCS, a second control signal ECS, a third control signal DCS, and a fourth control signal RCS.

[0067] The data driver **200** receives the third control signal DCS and the image data DATA from the driving controller **100**. The data driver **200** converts the image data DATA into data signals and outputs the data signals to a plurality of data lines DL**1** to DLm that are described further below. The data signals may be analog voltages corresponding to gray level values of the image data DATA. In an embodiment of the present disclosure, the data driver **200** may be embedded in the driver chip DIC illustrated in FIG. **2**A.

[0068] The scan driver **300** receives the first control signal SCS from the driving controller **100**. The scan driver **300** may output scan signals to scan lines in response to the first control signal SCS.

[0069] The voltage generator **400** generates voltages required for operation of the display panel DP. In the illustrated embodiment, the voltage generator **400** generates a first driving voltage ELVDD, a second driving voltage ELVSS, a first initialization voltage Vint, a second initialization voltage Vaint, a bias voltage Vbias, and a reset voltage Vrst.

[0070] The display panel DP may include a display area DA corresponding to the transmissive area TA (illustrated in FIG. **1**) and a non-display area NDA corresponding to the bezel area BZA (illustrated in FIG. **1**).

[0071] The display panel DP may include a plurality of pixels PX disposed in the display area DA and a plurality of sensors FX disposed in the display area DA. In an embodiment of the present disclosure, each of the sensors FX may be disposed between two pixels PX that are adjacent to each other. The pixels PX and the sensors FX may be arranged to alternate along the first and second directions DR**1** and DR**2**. However, the present disclosure is not limited thereto. That is, two or more pixels PX may be disposed between two sensors FX that are adjacent to each other in the first direction DR**1** among the plurality of sensors FX, or two or more pixels PX may be disposed between two sensors FX that are adjacent to each other in the second direction DR**2** among the plurality of sensors FX.

[0072] The display panel DP further includes initialization scan lines SIL**1** to SILn, compensation scan lines SCL**1** to SCLn, write scan lines SWL**1** to SWLn, black scan lines SBL**1** to SBLn, emission control lines EML**1** to EMLn, the data lines DL**1** to DLm, and readout lines RL**1** to RLh. The initialization scan lines SIL**1** to SILn, the compensation scan lines SCL**1** to SCLn, the write scan lines SWL**1** to SWLn, the black scan lines SBL**1** to SBLn, and the emission control lines EML**1** to EMLn extend in the first direction DR**1**. The initialization scan lines SIL**1** to SILn, the compensation scan lines SCL**1** to SCLn, the write scan lines SWL**1** to SWLn, the black scan lines SBL**1** to SBLn, and the emission control lines EML**1** to EMLn are arranged in the second direction DR**2** so as to be spaced apart from one another. The data lines DL**1** to DLm and the readout lines RL**1** to RLh extend in the second direction DR**2** and are arranged in the first direction DR**1** so as to be spaced apart from one another. Here, “n”, “m”, and “h” are natural numbers that are 1 or more.

[0073] The plurality of pixels PX are electrically connected to the initialization scan lines SIL**1** to SILn, the compensation scan lines SCL**1** to SCLn, the write scan lines SWL**1** to SWLn, the black scan lines SBL**1** to SBLn, the emission control lines EML**1** to EMLn, and the data lines DL**1** to DLm. For example, each of the plurality of pixels PX may be electrically connected to four scan lines. However, without being limited thereto, the number of scan lines connected to each pixel PX may be changed.

[0074] The plurality of sensors FX are electrically connected to the write scan lines SWL**1** to SWLn and the readout lines RL**1** to RLh. Each of the plurality of sensors FX may be electrically connected to one scan line. However, the present disclosure is not limited thereto. The number of scan lines connected to each sensor FX may be varied. In an embodiment of the present disclosure, the number of readout lines RL**1** to RLh may be smaller than or equal to the number of data lines DL**1** to DLm. For example, the number of readout lines RL**1** to RLh may correspond to ½, ¼, or ⅛ of the number of data lines DL**1** to DLm.

[0075] The scan driver **300** may be disposed in the non-display area NDA of the display panel DP. The scan driver **300** receives the first control signal SCS from the driving controller **100**. In response to the first control signal SCS, the scan driver **300** may output initialization scan signals to the initialization scan lines SIL**1** to SILn and may output compensation scan signals to the compensation scan lines SCL**1** to SCLn. Furthermore, in response to the first control signal SCS, the scan driver **300** may output write scan signals to the write scan lines SWL**1** to SWLn and may output black scan signals to the black scan lines SBL**1** to SBLn. Alternatively, the scan driver **300** may include first and second scan drivers. The first scan driver may output the initialization scan signals and the compensation scan signals, and the second scan driver may output the write scan signals and the black scan signals.

[0076] The emission driver **350** may be disposed in the non-display area NDA of the display panel DP. The emission driver **350** receives the second control signal ECS from the driving controller **100**. In response to the second control signal ECS, the emission driver **350** may output emission control signals to the emission control lines EML**1** to EMLn. Alternatively, the scan driver **300** may be connected to the emission control lines EML**1** to EMLn. In this case, the emission driver **350** may be omitted, and the scan driver **300** may output the emission control signals to the emission control lines EML**1** to EMLn.

[0077] The readout circuit **500** receives the fourth control signal RCS from the driving controller **100**. In response to the fourth control signal RCS, the readout circuit **500** may receive or process detection signals from the readout lines RL**1** to RLh. The readout circuit **500** may process the detection signals received from the readout lines RL**1** to RLh and may provide the processed detection signals S_FS to the driving controller **100**. The driving controller **100** may recognize biometric information based on the detection signals S_FS. In an embodiment of the present disclosure, the readout circuit **500** may be embedded in the sensor chips SIC**1** and SIC**2** illustrated in FIG. **2**A.

[0078] FIG. **4**A is a circuit diagram illustrating a pixel and a sensor according to an embodiment of the present disclosure, and FIG. **4**B is a waveform diagram showing emission and scan signals during operations of the pixel and the sensor illustrated in FIG. **4**A.

[0079] FIG. **4**A shows an equivalent circuit diagram of one pixel PXij among the plurality of pixels PX illustrated in FIG. **3**. Each of the pixels PX may have the same circuit structure, so that description of the circuit structure of the pixel PXij may apply all pixels PX, and detailed description of the other pixels will be omitted. FIG. **4**A further shows an equivalent circuit diagram of one sensor FXdj among the plurality of sensors FX illustrated in FIG. **3**. Each of the sensors FX may have the same circuit structure, so that description of the circuit structure of the sensor FXdj may apply to all sensors FX, and detailed description of the other sensors will be omitted.

[0080] Referring to FIG. **4**A, the pixel PXij is connected to the i-th data line DLi among the data lines DL**1** to DLm, the j-th initialization scan line SILj among the initialization scan lines SIL**1** to SILn, the j-th compensation scan line SCLj among the compensation scan lines SCL**1** to SCLn, the j-th write scan line SWLj among the write scan lines SWL**1** to SWLn, the j-th black scan line SBLj among the black scan lines SBL**1** to SBLn, and the j-th emission control line EMLj among the emission control lines EML**1** to EMLn.

[0081] The pixel PXij includes a light emitting element ED and a pixel driving circuit P_PD. The light emitting element ED may be a light emitting diode. In an embodiment of the present disclosure, the light emitting element ED may be an organic light emitting diode including an organic light emitting layer.

[0082] The pixel driving circuit P_PD includes first to eighth transistors T**1**, T**2**, T**3**, T**4**, T**5**, T**6**, T**7**, and T**8** and one capacitor Cst. At least one of the first to eighth transistors T**1** to T**8** may be a transistor having a low-temperature polycrystalline silicon (LTPS) semiconductor layer. Some of the first to eighth transistors T**1** to T**8** may be P-type transistors, and the others may be N-type transistors. At least one of the first to eighth transistors T**1** to T**8** may be a transistor having an oxide semiconductor layer. For example, the third and fourth transistors T**3** and T**4** may be oxide semiconductor transistors, and the first, second, and fifth to eighth transistors T**1**, T**2**, and T**5** to T**8** may be LTPS transistors. The third and fourth transistors T**3** and T**4** may be NMOS transistors.

[0083] The configuration of the pixel driving circuit P_PD according to the present disclosure is not limited to the embodiment illustrated in FIG. **4**A. The pixel driving circuit P_PD illustrated in FIG. **4**A is merely an example, and various changes and modifications may be made to the configuration of the pixel driving circuit P_PD. For example, the first, second, and fifth to eighth transistors T**1**, T**2**, and T**5** to T**8** may all be P-type transistors or N-type transistors.

[0084] The j-th initialization scan line SILj, the j-th compensation scan line SCLj, the j-th write scan line SWLj, the j-th black scan line SBLj, and the j-th emission control line EMLj may transfer the j-th initialization scan signal SIj, the j-th compensation scan signal SCj, the j-th write scan signal SWj, the j-th black scan signal SBj, and the j-th emission control signal EMj, respectively, to the pixel PXij. The i-th data line DLi transfers the i-th data signal Di to the pixel PXij. The i-th data signal Di may have a voltage level corresponding to the image signal RGB (refer to FIG. **3**) that is input to the display device DD (refer to FIG. **3**).

[0085] In an embodiment of the present disclosure, the pixel PXij may be connected to first and second driving voltage lines VL**1** and VL**2**, first and second initialization voltage lines VIL and

VAIL, and a bias voltage line VBL. The first driving voltage line VL**1** may transfer the first driving voltage ELVDD to the pixel PXij, and the second driving voltage line VL**2** may transfer the second driving voltage ELVSS to the pixel PXij. In addition, the first initialization voltage line VIL may transfer the first initialization voltage Vint to the pixel PXij, and the second initialization voltage line VAIL may transfer the second initialization voltage Vaint to the pixel PXij. The bias voltage line VBL may transfer the bias voltage Vbias to the pixel PXij.

[0086] The first transistor T**1** is connected between the first driving voltage line VL**1**, which receives the first driving voltage ELVDD, and the light emitting element ED. The first transistor T**1** includes a first electrode connected with the first driving voltage line VL**1** via the fifth transistor T**5**, a second electrode connected with an anode electrode of the light emitting element ED via the sixth transistor T**6**, and a third electrode (e.g., a gate electrode) connected with one end of the capacitor Cst (e.g., a first node N**1**). The first transistor T**1** may receive the i-th data signal Di that the i-th data line DLi transfers depending on a switching operation of the second transistor T**2** and may supply a driving current Id to an anode electrode of the light emitting element ED.

[0087] The second transistor T**2** is connected between the i-th data line DLi and the first electrode of the first transistor T**1**. The second transistor T**2** includes a first electrode connected with the i-th data line DLi, a second electrode connected with the first electrode of the first transistor T**1**, and a third electrode (e.g., a gate electrode) connected with the j-th write scan line SWLj. The second transistor T**2** may be turned on or off depending on the j-th write scan signal SWj transferred through the j-th write scan line SWLj and may transfer, to the first electrode of the first transistor T**1**, the i-th data signal Di from the i-th data line DLi.

[0088] The third transistor T**3** is connected between the second electrode of the first transistor T**1** and the first node N**1**. The third transistor T**3** includes a first electrode connected with the third electrode of the first transistor T**1**, a second electrode connected with the second electrode of the first transistor T**1**, and a third electrode (e.g., a gate electrode) connected with the j-th compensation scan line SCLj. The third transistor T**3** may be turned on or off depending on the j-th compensation scan signal SCj transferred through the j-th compensation scan line SCLj and may connect the first transistor T**1** in the form of a diode by connecting the third electrode and the second electrode of the first transistor T**1**.

[0089] The fourth transistor T**4** is connected between the first initialization voltage line VIL to which the first initialization voltage Vint is applied and the first node N**1**. The fourth transistor T**4** includes a first electrode connected with the first initialization voltage line VIL through which the first initialization voltage Vint is transferred, a second electrode connected with the first node N**1**, and a third electrode (e.g., a gate electrode) connected with the j-th initialization scan line SILj. The fourth transistor T**4** is turned on or off depending on the j-th initialization scan signal SIj transferred through the j-th initialization scan line SILj. The turned-on fourth transistor T**4** initializes the potential of the third electrode of the first transistor T**1** (that is, the potential of the first node N**1**) by transferring the first initialization voltage Vint to the first node N**1**.

[0090] The fifth transistor T**5** includes a first electrode connected with the first driving voltage line VL**1**, a second electrode connected with the first electrode of the first transistor T**1**, and a third electrode (e.g., a gate electrode) connected to the j-th emission control line EMLj.

[0091] The sixth transistor T**6** includes a first electrode connected with the second electrode of the first transistor T**1**, a second electrode connected to the anode electrode of the light emitting element ED, and a third electrode (e.g., a gate electrode) connected to the j-th emission control line EMLj.

[0092] The fifth and sixth transistors T**5** and T**6** are simultaneously turned on or off depending on the j-th emission control signal EMj transferred through the j-th emission control line EMLj. The first driving voltage ELVDD applied through the turned-on fifth transistor T**5** may be compensated for through the first transistor T**1** connected in the form of a diode and thereafter may be transferred to the light emitting element ED.

[0093] The seventh transistor T**7** includes a first electrode connected to the second initialization

voltage line VAIL through which the second initialization voltage Vaint is transferred, a second electrode connected with the second electrode of the sixth transistor T**6**, and a third electrode (e.g., a gate electrode) connected with the j-th black scan line SBLj. The second initialization voltage Vaint may have a voltage level lower than or equal to the voltage level of the first initialization voltage Vint.

[0094] The eighth transistor T**8** includes a first electrode connected to the bias voltage line VBL through which the bias voltage Vbias is transferred, a second electrode connected with the first electrode of the first transistor T**1**, and a third electrode (e.g., a gate electrode) connected with the j-th black scan line SBLj.

[0095] The seventh and eighth transistors T**7** and T**8** are simultaneously turned on or off depending on the j-th black scan signal SBj transferred through the j-th black scan line SBLj. The second initialization voltage Vaint applied through the turned-on seventh transistor T**7** may be transferred to the anode electrode of the light emitting element ED. Accordingly, the anode electrode of the light emitting element ED may be initialized to the second initialization voltage Vaint. The bias voltage Vbias applied through the turned-on eighth transistor T**8** may be transferred to the first electrode of the first transistor T**1**. Accordingly, the bias voltage Vbias may be periodically applied to the first electrode of the first transistor T**1**. As a result, deterioration in display quality due to an increase in the potential difference between the first and second electrodes of the first transistor T**1** to a certain level or higher by a magnetic hysteresis phenomenon may be prevented.

[0096] The one end of the capacitor Cst is connected with the third electrode of the first transistor T**1** as described above, and the opposite end of the capacitor Cst is connected with the first driving voltage line VL**1**. A cathode electrode of the light emitting element ED may be connected with the second driving voltage line VL**2** that transfers the second driving voltage ELVSS. The second driving voltage ELVSS may have a lower voltage level than the first driving voltage ELVDD. In an embodiment of the present disclosure, the second driving voltage ELVSS may have a lower voltage level than the first and second initialization voltages Vint and Vaint.

[0097] Referring to FIGS. **4**A and **4**B, the j-th emission control signal EMj has a high level during a non-light emission period NEP. Within the non-light emission period NEP, the j-th initialization scan signal SIj is activated, e.g., to a high level. When the j-th initialization scan signal SIj having the high level is provided through the j-th initialization scan line SILj during an activation period AP**1** (hereinafter, referred to as a first activation period) of the j-th initialization scan signal SIj, the fourth transistor T**4** turns on in response to the j-th initialization scan signal SIj having the high level. The first initialization voltage Vint is transferred to the third electrode of the first transistor T**1** through the turned-on fourth transistor T**4**, and the first node N**1** is initialized to the first initialization voltage Vint. Accordingly, the first activation period AP**1** may be defined as an initialization period of the pixel PXij.

[0098] Next, when the j-th compensation scan signal SCj is activated and the j-th compensation scan signal SCj having a high level is supplied through the j-th compensation scan line SCLj during an activation period AP**2** (hereinafter, referred to as a second activation period) of the j-th compensation scan signal SCj, the third transistor T**3** is turned on. The third transistor T**3** when turned on connects the first transistor T**1** in the form of a diode that is forward-biased. The first activation period AP**1** may not overlap the second activation period AP**2**.

[0099] Within the second activation period AP**2**, the j-th write scan signal SWj is activated. The j-th write scan signal SWj has a low level during an activation period AP**4** (hereinafter, referred to as a fourth activation period). During the fourth activation period AP**4**, the second transistor T**2** is turned on by the j-th write scan signal SWj having the low level. Then, a compensation voltage "Di-Vth" obtained by subtracting the threshold voltage Vth of the first transistor T**1** from the i-th data signal Di supplied from the i-th data line DLi is applied to the third electrode of the first transistor T**1**. That is, the potential of the third electrode of the first transistor T**1** may be the compensation voltage "Di-Vth". The fourth activation period AP**4** may overlap the second

activation period AP**2**. The duration time of the second activation period AP**2** may be greater than the duration time of the fourth activation period AP**4**.
[0100] The first driving voltage ELVDD and the compensation voltage “Di-Vth” may be applied to the opposite ends of the capacitor Cst, and charges corresponding to a difference between voltages at the opposite ends of the capacitor Cst may be stored in the capacitor Cst. Here, the period during which the j-th compensation scan signal SCj has the high level may be referred to as a compensation period of the pixel PXij.
[0101] Meanwhile, the j-th black scan signal SBj is activated within the second activation period AP**2** of the j-th compensation scan signal SCj. The j-th black scan signal SBj has a low level during an activation period AP**3** (hereinafter, referred to as a third activation period). During the third activation period AP**3**, the seventh transistor T**7** is turned on by receiving the j-th black scan signal SBj having the low level through the j-th black scan line SBLj. A portion of the driving current Id may escape through the seventh transistor T**7** as a bypass current Ibp. The third activation period AP**3** may overlap the second activation period AP**2**. The duration time of the second activation period AP**2** may be greater than the duration time of the third activation period AP**3**. The third activation period AP**3** may precede the fourth activation period AP**4** and may not overlap the fourth activation period AP**4**.
[0102] When the pixel PXij displays a black image, the pixel PXij is not able to normally display the black image if the light emitting element ED emits light even though the minimum driving current of the first transistor T**1** flows as the driving current Id. Accordingly, the seventh transistor T**7** in the pixel PXij according to an embodiment of the present disclosure may distribute a portion of the minimum driving current of the first transistor T**1** as the bypass current Ibp to a current path other than the current path toward the light emitting element ED. Here, the minimum driving current of the first transistor T**1** means a current flowing to the first transistor T**1** under the condition that a gate-source voltage Vgs of the first transistor T**1** is lower than the threshold voltage Vth so that the first transistor T**1** is turned off. The minimum driving current (e.g., a current of about 10 pA or less) flowing to the first transistor T**1** under the condition that the first transistor T**1** is turned off is transferred to the light emitting element ED, and a black gray-scale image is displayed. When the pixel PXij displays the black image, an influence of the bypass current Ibp on the minimum driving current is relatively great, whereas when the pixel PXij displays an image such as a general image or a white image, the bypass current Ibp has little influence on the driving current Id. Accordingly, when the pixel PXij displays the black image, the current obtained by subtracting the bypass current Ibp escaping through the seventh transistor T**7** from the driving current Id (that is, a light emission current led) may be provided to the light emitting element ED so that the pixel PXij may clearly express the black image. Thus, the pixel PXij may implement an accurate black in a gray-scale image using the seventh transistor T**7**, thereby improving the contrast ratio.
[0103] After that, the j-th emission control signal EMj supplied from the j-th emission control line EMLj is changed from the high level to a low level. The fifth and sixth transistors T**5** and T**6** are turned on by the emission control signal EMj having the low level. Then, the driving current Id depending on the difference between the voltage of the third electrode of the first transistor T**1** and the first driving voltage ELVDD is generated. The driving current Id is supplied to the light emitting element ED through the sixth transistor T**6**, and the light emission current led flows through the light emitting element ED.
[0104] Referring again to FIG. **4**A, the sensor FXdj is connected to the d-th readout line RLd among the readout lines RL**1** to RLh, the j-th write scan line SWLj, and a reset control line SRL.
[0105] The sensor FXdj includes a light receiving element OPD and a sensor driving circuit O_SD. In an embodiment of the present disclosure, the light receiving element OPD may be an organic photo diode including an organic material as a photoelectric conversion layer. Although FIG. **4**A illustrates the structure in which the sensor FXdj includes one light receiving element, the present

disclosure is not limited thereto. For example, the sensor FXdj may include a plurality of light receiving elements OPD connected in parallel.

[0106] An anode electrode of the light receiving element OPD may be connected to a first sensing node SN**1**, and a cathode electrode of the light receiving element OPD may be connected with the second driving voltage line VL**2** that transfers the second driving voltage ELVSS. The cathode electrode of the light receiving element OPD may be electrically connected with the cathode electrode of the light emitting element ED. In an embodiment of the present disclosure, the cathode electrode of the light receiving element OPD may be integrally formed with the cathode electrode of the light emitting element ED and may form a common cathode electrode C_CE (refer to FIG. **6**).

[0107] The sensor driving circuit O_SD includes three transistors ST**1**, ST**2**, and ST**3**. The three transistors ST**1**, ST**2**, and ST**3** may be the reset transistor ST**1**, the amplifying transistor ST**2**, and the output transistor ST**3**, respectively. At least one of the reset transistor ST**1**, the amplifying transistor ST**2**, and the output transistor ST**3** may be an oxide semiconductor transistor. In an embodiment of the present disclosure, the reset transistor ST**1** may be an oxide semiconductor transistor, and the amplifying transistor ST**2** and the output transistor ST**3** may be LTPS transistors. However, without being limited thereto, the reset transistor ST**1** and the output transistor ST**3** may be oxide semiconductor transistors, and the amplifying transistor ST**2** may be an LTPS transistor.

[0108] Some of the reset transistor ST**1**, the amplifying transistor ST**2**, and the output transistor ST**3** may be P-type transistors, and the rest may be N-type transistors. In an embodiment of the present disclosure, the amplifying transistor ST**2** and the output transistor ST**3** may be PMOS transistors, and the reset transistor ST**1** may be an NMOS transistor. However, without being limited thereto, the reset transistor ST**1**, the amplifying transistor ST**2**, and the output transistor ST**3** may all be N-type transistors or P-type transistors.

[0109] One or more (e.g., the reset transistor ST**1**) of the reset transistor ST**1**, the amplifying transistor ST**2**, and the output transistor ST**3** may be of the same type as the third and fourth transistors T**3** and T**4** of the pixel PXij. The amplifying transistor ST**2** and the output transistor ST**3** may be transistors of the same type as the first, second, and fifth to eighth transistors T**1**, T**2**, and T**5** to T**8** of the pixel PXij.

[0110] The circuit configuration of the sensor driving circuit O_SD according to the present disclosure is not limited to that illustrated in FIG. **4**A. FIG. **4**A merely shows an example embodiment of the sensor driving circuit O_SD, and various changes and modifications may be made to the configuration of the sensor driving circuit O_SD.

[0111] In the embodiment of FIG. **4**A, the reset transistor ST**1** includes a first electrode that receives the reset voltage Vrst, a second electrode connected with the first sensing node SN**1**, and a third electrode (e.g., a gate electrode) that receives a reset control signal SR. The reset transistor ST**1** may reset the potential of the first sensing node SN**1** to the reset voltage Vrst in response to the reset control signal SR. The reset control signal SR may be a signal provided through the reset control line SRL. However, the present disclosure is not limited thereto. Alternatively, the reset control signal SR may be the j-th compensation scan signal SCj supplied through the j-th compensation scan line SCLj. That is, the reset transistor ST**1** may receive the j-th compensation scan signal SCj, which is supplied from the j-th compensation scan line SCLj, as the reset control signal SR. In an embodiment of the present disclosure, the reset voltage Vrst may have a lower voltage level than the second driving voltage ELVSS at least during an activation period of the reset control signal SR. The reset voltage Vrst may be transferred to the sensor FXdj through a reset voltage line VRL. The reset voltage Vrst may be a DC voltage maintained at a voltage level lower than that of the second driving voltage ELVSS.

[0112] The reset transistor ST**1** may include a plurality of sub-reset transistors connected in series. For example, the reset transistor ST**1** may include two sub-reset transistors (hereinafter, referred to as the first and second sub-reset transistors). In this case, a third electrode of the first sub-reset

transistor and a third electrode of the second sub-reset transistor are connected to the reset control line SRL. Furthermore, a second electrode of the first sub-reset transistor and a first electrode of the second sub-reset transistor may be electrically connected with each other. In addition, the reset voltage Vrst may be applied to a first electrode of the first sub-reset transistor, and a second electrode of the second sub-reset transistor may be electrically connected with the first sensing node SN**1**. However, the number of sub-reset transistors is not limited thereto and may be modified in various ways.

[0113] The amplifying transistor ST**2** includes a first electrode that receives a sensing driving voltage SLVD, a second electrode connected with a second sensing node SN**2**, and a third electrode (e.g., a gate electrode) connected with the first sensing node SN**1**. The amplifying transistor ST**2** may be turned on depending on the potential of the first sensing node SN**1** and may apply the sensing driving voltage SLVD to the second sensing node SN**2**. In an embodiment of the present disclosure, the sensing driving voltage SLVD may be one of the first driving voltage ELVDD, the first initialization voltage Vint, and the second initialization voltage Vaint. When the sensing driving voltage SLVD is the first driving voltage ELVDD, the first electrode of the amplifying transistor ST**2** may be electrically connected to the first driving voltage line VL**1**. When the sensing driving voltage SLVD is the first initialization voltage Vint, the first electrode of the amplifying transistor ST**2** may be electrically connected to the first initialization voltage line VIL, and when the sensing driving voltage SLVD is the second initialization voltage Vaint, the first electrode of the amplifying transistor ST**2** may be electrically connected to the second initialization voltage line VAIL.

[0114] The output transistor ST**3** includes a first electrode connected with the second sensing node SN**2**, a second electrode connected with the d-th readout line RLd, and a third electrode that receives an output control signal. In response to the output control signal, the output transistor ST**3** may transfer a detection signal FSd to the d-th readout line RLd. The output control signal may be the j-th write scan signal SWj supplied through the j-th write scan line SWLj. That is, the output transistor ST**3** may receive the j-th write scan signal SWj, which is supplied from the j-th write scan line SWLj, as the output control signal.

[0115] The light receiving element OPD of the sensor FXdj may be exposed to light during a light emission period of the light emitting element ED. The light may be light output from the light emitting element ED.

[0116] If the user's hand US_F (refer to FIG. **1**) touches the display surface IS (refer to FIG. **1**), the light receiving element OPD generates photo-charges corresponding to light reflected by ridges of a fingerprint or valleys between the ridges. The amount of current flowing through the light receiving element OPD varies depending on the generated photo-charges. When the light receiving element OPD receives light reflected by the ridges of the fingerprint, a current flowing through the light receiving element OPD may be referred to as a first current, and when the light receiving element OPD receives light reflected by the valleys of the fingerprint, a current flowing through the light receiving element OPD may be referred to as a second current The amount of light reflected by the ridges of the fingerprint and the amount of light reflected by the valleys of the fingerprint are different from each other, and the difference between the amounts of light appears as a difference between the first and second currents. When the first current flows through the light receiving element OPD, the potential of the first sensing node SN**1** may be referred to as a first potential, and when the second current flows through the light receiving element OPD, the potential of the first sensing node SN**1** may be referred to as a second potential. In an embodiment of the present disclosure, the first current may be greater than the second current. In this case, the first potential may be lower than the second potential.

[0117] The amplifying transistor ST**2** may be a source follower amplifier that generates a source-drain current in proportion to the potential of the first sensing node SN**1** that is input to the third electrode.

[0118] During the fourth activation period AP**4**, the j-th write scan signal SWj having the low level is supplied to the output transistor ST**3** through the j-th write scan line SWLj. When the output transistor ST**3** is turned on in response to the j-th write scan signal SWj having the low level, the detection signal FSd corresponding to a current flowing through the amplifying transistor ST**2** may be output to the d-th readout line RLd.
[0119] When the reset control signal SR having a high level is supplied through the reset control line SRL during a reset period, the reset transistor ST**1** is turned on. The reset period may be defined as an activation period (that is, a high-level period) of the reset control signal SR. Alternatively, when the reset transistor ST**1** is implemented with a P-type transistor, the reset control signal SR having a low level may be supplied to the reset control line SRL during the reset period. The first sensing node SN**1** may be reset to a potential corresponding to the reset voltage Vrst during the reset period. In an embodiment of the present disclosure, the reset voltage Vrst may have a lower voltage level than the second driving voltage ELVSS.
[0120] When the reset period ends, the light receiving element OPD may generate photo-charges corresponding to received light, and the generated photo-charges may accumulate in the first sensing node SN**1**.
[0121] FIG. **5**A is a plan view of the display panel according to an embodiment of the present disclosure. FIG. **5**B is an enlarged view of a portion of the display panel illustrated in FIG. **5**A. For convenience of description and illustration clarity, FIG. **5**A only shows the data lines and the readout lines and does not show the scan lines and the emission control lines.
[0122] Referring to FIG. **5**A, the display panel DP includes the display area DA and the non-display area NDA. The plurality of pixels PX (refer to FIG. **3**) and the plurality of sensors FX (refer to FIG. **3**) are in the display area DA. The driver chip DIC and the sensor chips SIC**1** and SIC**2** are mounted on the non-display area NDA.
[0123] The data lines DL**1** to DLm (refer to FIG. **3**) are connected to the plurality of pixels PX in the display area DA and connected to the driver chip DIC in the non-display area NDA. The readout lines RL**1** to RLh (refer to FIG. **3**) are connected to the plurality of sensors FX in the display area DA and connected to the sensor chips SIC**1** and SIC**2** in the non-display area NDA.
[0124] The data lines DL**1** to DLm may be divided into a first group and a second group. The first group includes a plurality of first data lines DL_G**1**, and the second group includes a plurality of second data lines DL_G**2**. The plurality of first data lines DL_G**1** are space apart from each other along the first direction DR**1**, and the plurality of second data lines DL_G**2** are spaced apart from each other along the first direction DR**1**. The plurality of first data lines DL_G**1** are spaced apart from the plurality of second data lines DL_G**2** in the first direction DR**1**.
[0125] The plurality of first data lines DL_G**1** are connected to pixel driving circuits P_PD of a first group of pixels among the plurality of pixels PX, and the plurality of second data lines DL_G**2** are connected to pixel driving circuits P_PD of a second group of pixels among the plurality of pixels PX. The first group of pixels and the first data lines DL_G**1** are disposed in a first area A**1**, and the second group of pixels and the second data lines DL_G**2** are disposed in a second area A**2**. The first area A**1** includes a first-first area A**1-1** that is on a first side with respect to a center line of the display panel DP that is parallel to the second direction DR**2** and a first-second area A**1-2** that is on a second side with respect to the center line. The second area A**2** includes a second-first area A**2-1** disposed between the first-first area A**1-1** and the non-display area NDA and a second-second area A**2-2** disposed between the first-second area A**1-2** and the non-display area NDA.
[0126] The plurality of first data lines DL_G**1** include first-first data lines DL**1-1** in the first-first area A**1-1** and first-second data lines DL**1-2** in the first-second area A**1-2**. The plurality of second data lines DL_G**2** include second-first data lines DL**2-1** in the second-first area A**2-1** and second-second data lines DL**2-2** in the second-second area A**2-2**.
[0127] The first-first data lines DL**1-1** and the first-second data lines DL**1-2** are connected to the driver chip DIC. Although FIG. **5**A illustrates an example that the first-first data lines DL**1-1** and

the first-second data lines DL**1-2** are connected to the same driver chip DIC, the present disclosure is not limited thereto. For example, the first-first data lines DL**1-1** and the first-second data lines DL**1-2** may be connected to different driver chips, respectively.

[0128] The display panel DP further includes data connecting lines that connect the second data lines DL_G**2** to the driver chip DIC. The data connecting lines include a plurality of vertical data connecting lines V_DCL extending in the second direction DR**2** along the first data lines DL_G**1** and a plurality of horizontal data connecting lines H_DCL extending in the first direction DR**1**.

[0129] The plurality of horizontal data connecting lines H_DCL include first horizontal data connecting lines H_DCL**11** to H_DCL**13** and second horizontal data connecting lines H_DCL**21** to H_DCL**23**. The first horizontal data connecting lines H_DCL**11** to H_DCL**13** are connected with the second-first data lines DL**2-1**, and the second horizontal data connecting lines H_DCL**21** to H_DCL**23** are connected with the second-second data lines DL**2-2**. The plurality of vertical data connecting lines V_DCL include first vertical data connecting lines V_DCL**1** and second vertical data connecting lines V_DCL**2**. The first vertical data connecting lines V_DCL**1** are connected to the first horizontal data connecting lines H_DCL**11** to H_DCL**13**, and the second vertical data connecting lines V_DCL**2** are connected with the second horizontal data connecting lines H_DCL**21** to H_DCL**23**.

[0130] Accordingly, the first vertical data connecting lines V_DCL**1** are electrically connected with the second-first data lines DL**2-1** by the first horizontal data connecting lines H_DCL**11** to H_DCL**13**. The second vertical data connecting lines V_DCL**2** are electrically connected with the second-second data lines DL**2-2** by the second horizontal data connecting lines H_DCL**21** to H_DCL**23**.

[0131] The first vertical data connecting lines V_DCL**1** alternate with the first-first data lines DL**1-1** in the first-first area A**1-1**. The second vertical data connecting lines V_DCL**2** alternate with the first-second data lines DL**1-2** in the first-second area A**1-2**.

[0132] The plurality of horizontal data connecting lines H_DCL and portions of the vertical data connecting lines V_DCL may be in the display area DA. That is, portions of the data connecting lines for connecting the second data lines DL_G**2** and the driver chip DIC are disposed in the display area DA. Accordingly, the area of the region occupied by the data connecting lines in the non-display area NDA may be decreased, and thus the area of dead space of the display panel DP may be decreased.

[0133] The readout lines RL**1** to RLh may be divided into a first group and a second group. The first group includes a plurality of first readout lines RL_G**1**, and the second group includes a plurality of second readout lines RL_G**2**. The plurality of first readout lines RL_G**1** are spaced apart along the first direction DR**1**, and the plurality of second readout lines RL_G**2** are space apart along the first direction DR**1**. The plurality of first readout lines RL_G**1** are spaced apart from the plurality of second readout lines RL_G**2** in the first direction DR**1**.

[0134] The plurality of first readout lines RL_G**1** are connected to sensor driving circuits O_SD of a first group of sensors among the plurality of sensors FX, and the plurality of second readout lines RL_G**2** are connected to sensor driving circuits O_SD of a second group of sensors among the plurality of sensors FX. The first group of sensors and the first readout lines RL_G**1** are in the second area A**2**, and the second group of sensors and the second readout lines RL_G**2** are in the first area A**1**.

[0135] The plurality of first readout lines RL_G**1** include first-first readout lines RL**1-11** to RL**1-13** and first-second readout lines RL**1-21** to RL**1-23**. The first-first readout lines RL**1-11** to RL**1-23** are in the second-first area A**2-1** and connected to the first sensor chip SIC**1**. The first-second readout lines RL**1-21** to RL**1-23** are in the second-second area A**2-2** and connected to the second sensor chip SIC**2**.

[0136] The plurality of second readout lines RL_G**2** include second-first readout lines RL**2-11** to RL**2-13** and second-second readout lines RL**2-21** to RL**2-23**. The second-first readout lines RL**2-11**

to RL**2-13** are in the first-first area A**1-1** and electrically connected to the first sensor chip SIC**1**. The second-second readout lines RL**2-21** to RL**2-23** are in the first-second area A**1-2** and electrically connected to the second sensor chip SIC**2**. The plurality of second readout lines RL_G**2** may be between the first-first readout lines RL**1-11** to RL**1-13** and the first-second readout lines RL**1-21** to RL**1-23**.

[0137] The display panel DP further includes connecting lines electrically connected with the second readout lines RL_G**2**. The connecting lines include a plurality of vertical connecting lines V_RL extending in the second direction DR**2** along the first readout lines RL_G**1** and a plurality of horizontal connecting lines H_RL extending in the first direction DR**1**. The vertical connecting lines V_RL may include first vertical connecting lines V_RL**1** electrically connected to the first sensor chip SIC**1** and second vertical connecting lines V_RL**2** electrically connected to the second sensor chip SIC**2**.

[0138] The first vertical connecting lines V_RL**1** may alternate with the first-first readout lines RL**1-11** to RL**1-13** in the first direction DR**1**. The second vertical connecting lines V_RL**2** may alternate with the first-second readout lines RL**1-21** to RL**1-23** in the first direction DR**1**.

[0139] The horizontal connecting lines H_RL electrically connect the vertical connecting lines V_RL to the second readout lines RL_G**2**. The horizontal connecting lines H_RL include first horizontal connecting lines H_RL**1** that respectively connect the first vertical connecting lines V_RL**1** to the second-first readout lines RL**2-11** to RL**2-13**, and second horizontal connecting lines H_RL**2** that respectively connect the second vertical connecting lines V_RL**2** to the second-second readout lines RL**2-21** to RL**2-23**.

[0140] The plurality of horizontal connecting lines H_RL and portions of the vertical connecting lines V_RL may be disposed in the display area DA. That is, portions of the connecting lines for connecting the second readout lines RL_G**2** and the first and second sensor chips SIC**1** and SIC**2** are disposed in the display area DA. Accordingly, the area of the region occupied by the connecting lines in the non-display area NDA may be decreased, and thus the area of dead space of the display panel DP may be decreased.

[0141] Even though the first or second sensor chip SIC**1** or SIC**2** is disposed adjacent to the driver chip DIC, the readout lines and the data lines may not cross each other in the non-display area NDA when the second readout lines RL_G**2** are connected to the first or second sensor chip SIC**1** or SIC**2** through the connecting lines and the second data lines DL_G**2** are connected to the driver chip DIC through the data connecting lines. Accordingly, coupling capacitance between the readout lines and the data lines may be decreased, and thus the sensing accuracy of the sensors FX may be improved.

[0142] Referring to FIG. **5**B, the first readout lines RL_G**1** and the second readout lines RL_G**2** may cross the scan lines SIL**1** to SILn, SCL**1** to SCLn, SWL**1** to SWLn, and SBL**1** to SBLn (refer to FIG. **3**) and the emission control lines EML**1** to EMLn (refer to FIG. **3**) that extend in the first direction DR**1**.

[0143] In an embodiment of the present disclosure, the first-first readout lines RL**1-11** to RL**1-13** may cross the j-th initialization scan line SILj, the j-th compensation scan line SCLj, the j-th write scan line SWLj, the j-th black scan line SBLj, and the j-th emission control line EMLj once. Likewise, the second-first readout lines RL**2-11** to RL**2-13** may cross the j-th initialization scan line SILj, the j-th compensation scan line SCLj, the j-th write scan line SWLj, the j-th black scan line SBLj, and the j-th emission control line EMLj once.

[0144] First coupling capacitance Ccp**1** may be formed at the intersection points where the first-first readout lines RL**1-11** to RL**1-13** cross the scan lines SIL**1** to SILn, SCL**1** to SCLn, SWL**1** to SWLn, and SBL**1** to SBLn and the emission control lines EML**1** to EMLn, and second coupling capacitance Ccp**2** may be formed at the intersection points where the second-first readout lines RL**2-11** to RL**2-13** cross the scan lines SIL**1** to SILn, SCL**1** to SCLn, SWL**1** to SWLn, and SBL**1** to SBLn and the emission control lines EML**1** to EMLn.

[0145] In an embodiment of the present disclosure, the second-first readout lines RL**2**-**11** to RL**2**-**13** are connected to the first vertical connecting lines V_RL**1** through the first horizontal connecting lines H_RL**1**. Since the first horizontal connecting lines H_RL**1** extend in the first direction DR**1**, the first horizontal connecting lines H_RL**1** do not cross the j-th initialization scan line SILj, the j-th compensation scan line SCLj, the j-th write scan line SWLj, the j-th black scan line SBLj, and the j-th emission control line EMLj. However, since the first vertical connecting lines V_RL**1** extend in the second direction DR**2**, the first vertical connecting lines V_RL**1** may cross the j-th initialization scan line SILj, the j-th compensation scan line SCLj, the j-th write scan line SWLj, the j-th black scan line SBLj, and the j-th emission control line EMLj. Accordingly, third coupling capacitance Ccp**3** may be formed at the intersection points where the first vertical connecting lines V_RL**1** cross the scan lines SIL**1** to SILn, SCL**1** to SCLn, SWL**1** to SWLn, and SBL**1** to SBLn and the emission control lines EML**1** to EMLn.
[0146] Thus, only the first coupling capacitance Ccp**1** may act on the first-first readout lines RL**1**-**11** to RL**1**-**13**, but the second coupling capacitance Ccp**2** and the third coupling capacitance Ccp**3** may act on the second-first readout lines RL**2**-**11** to RL**2**-**13**. The difference between the coupling capacitance acting on the second-first readout lines RL**2**-**11** to RL**2**-**12** and the coupling capacitance acting on the first-first readout lines RL**1**-**11** to RL**1**-**13** may be reduced when the third coupling capacitance Ccp**3** is decreased.
[0147] A method of decreasing the third coupling capacitance Ccp**3** by applying a shielding pattern is described below with reference to FIGS. **7**A to **8**C.
[0148] FIG. **6** is a sectional view of the display panel according to an embodiment of the present disclosure.
[0149] Referring to FIG. **6**, the display panel DP may include the base layer BL, the circuit layer DP_CL, and the element layer DP_ED.
[0150] The base layer BL may include a synthetic resin layer. The synthetic resin layer may include a thermosetting resin. In particular, the synthetic resin layer may be a polyimide-based resin layer, but the material thereof is not particularly limited. The synthetic resin layer may include at least one of an acrylic resin, a methacrylic resin, a polyisoprene resin, a vinyl resin, an epoxy resin, a urethane-based resin, a celluosic resin, a siloxane-based resin, a polyamide resin, or a perylene-based resin. In addition, the base layer BL may include a glass substrate, a metal substrate, or an organic/inorganic composite substrate.
[0151] At least one inorganic layer is formed on the upper surface of the base layer BL. The inorganic layer may include at least one of aluminum oxide, titanium oxide, silicon oxide, silicon oxy nitride, zirconium oxide, or hafnium oxide. The inorganic layer may be formed of multiple layers. The multiple inorganic layers may constitute a barrier layer BRL and/or a buffer layer BFL that are described below. The barrier layer BRL and the buffer layer BFL may be selectively disposed or patterned.
[0152] The circuit layer DP_CL may include the barrier layer BRL and/or the buffer layer BFL. The barrier layer BRL prevents infiltration of foreign matter from the base layer or otherwise outside the display panel DP. The barrier layer BRL may include a silicon oxide layer and a silicon nitride layer. A plurality of silicon oxide layers and a plurality of silicon nitride layers may be provided. The silicon oxide layers and the silicon nitride layers may be alternately stacked one above another.
[0153] The buffer layer BFL may be disposed on the barrier layer BRL. The buffer layer BFL may improve the coupling force between the base layer BL and a semiconductor pattern and/or a conductive pattern in the circuit layer DP_CL. The buffer layer BFL may include silicon oxide layers and silicon nitride layers. The silicon oxide layers and the silicon nitride layers may be alternately stacked one above another.
[0154] The semiconductor pattern is on the buffer layer BFL. Hereinafter, the semiconductor pattern directly on the buffer layer BFL or otherwise closest to the base layer BL is referred to as a

first semiconductor pattern. The first semiconductor pattern may include a silicon semiconductor. The first semiconductor pattern may include polysilicon. However, without being limited thereto, the first semiconductor pattern may include amorphous silicon.

[0155] FIG. **6** merely illustrates a portion of the first semiconductor pattern, and the first semiconductor pattern may be additionally in another area of the pixel PXij (refer to FIG. **4**A) or other pixels PX or sensors FX. The first semiconductor pattern may have different electrical properties depending on whether or not an area of the first semiconductor pattern is doped. The first semiconductor pattern may include a doped area and a non-doped area. The doped area may be doped with an N-type dopant or a P-type dopant. A P-type transistor includes a doped area doped with a P-type dopant, and an N-type transistor includes a doped area doped with an N-type dopant.

[0156] The doped area has a higher conductivity than the non-doped area and may serve as an electrode or a signal line. The non-doped area substantially may correspond to an active area (or, a channel) of a transistor. In other words, one portion of the first semiconductor pattern may be the active area of the transistor, another portion may be a source or drain of the transistor, and another portion may be a connecting signal line or a connecting electrode.

[0157] As illustrated in FIG. **6**, a first electrode S**1**, a channel part A**1**, and a second electrode D**1** of the first transistor T**1** may be formed in the first semiconductor pattern. The first electrode S**1** and the second electrode D**1** of the first transistor T**1** extend from the channel part A**1** in opposite directions.

[0158] In FIG. **6**, a portion of a connecting signal line CSL formed from the semiconductor pattern is illustrated. Although not separately illustrated, the connecting signal line CSL may be connected to the second electrode of the sixth transistor T**6** (refer to FIG. **4**A) when viewed from above the plane.

[0159] A first insulating layer **10** is on the buffer layer BFL. The first insulating layer **10** commonly overlaps the plurality of pixels PX (refer to FIG. **3**) and covers the first semiconductor pattern. The first insulating layer **10** may be an inorganic layer and/or an organic layer and may have a single-layer structure or a multi-layer structure. The first insulating layer **10** may include at least one of aluminum oxide, titanium oxide, silicon oxide, silicon oxynitride, zirconium oxide, or hafnium oxide. In an example embodiment, the first insulating layer **10** may be a single silicon oxide layer. Not only the first insulating layer **10** but also insulating layers of the circuit layer DP_CL that are described below may be inorganic layers and/or organic layers, and each may have a single-layer structure or a multi-layer structure. The inorganic layers may include at least one of the aforementioned materials.

[0160] The third electrode G**1** of the first transistor T**1** is disposed on the first insulating layer **10**. The third electrode G**1** may be a portion of a first gate pattern layer GAT**1** (refer to FIG. **9**B). The third electrode G**1** of the first transistor T**1** overlaps the channel part A**1** of the first transistor T**1**. The third electrode G**1** of the first transistor T**1** may serve as a mask in a process of doping the first semiconductor pattern.

[0161] A second insulating layer **20** that covers the third electrode G**1** is on the first insulating layer **10**. The second insulating layer **20** commonly overlaps the plurality of pixels PX. The second insulating layer **20** may be an inorganic layer and/or an organic layer and may have a single-layer structure or a multi-layer structure. In the example embodiment, the second insulating layer **20** may be a single silicon oxide layer.

[0162] An upper electrode UE may be on the second insulating layer **20**. The upper electrode UE may overlap the third electrode G**1**. The upper electrode UE may a portion of a second gate pattern layer GAT**2** (refer to FIG. **9**C) or may be a portion of a doped semiconductor pattern. A portion of the third electrode G**1** and the upper electrode UE overlapping the portion of the third electrode G**1** may define the capacitor Cst (refer to FIG. **4**A). In an embodiment of the present disclosure, the upper electrode UE may be omitted.

[0163] In an embodiment of the present disclosure, the second insulating layer **20** may be replaced

with an insulating pattern, and the upper electrode UE may be on the insulating pattern. The upper electrode UE may serve as a mask during a process that forms the insulating pattern from the second insulating layer **20**.

[0164] A third insulating layer **30** that covers the upper electrode UE is on the second insulating layer **20**. In the example embodiment, the third insulating layer **30** may be a single silicon oxide layer. A semiconductor pattern is on the third insulating layer **30**. Hereinafter, the semiconductor pattern directly on the third insulating layer **30** may be referred to as a second semiconductor pattern. The second semiconductor pattern may include metal oxide semiconductor. The oxide semiconductor may include a crystalline or amorphous oxide semiconductor. For example, the oxide semiconductor may include metal oxide of zinc (Zn), indium (In), gallium (Ga), tin (Sn), or titanium (Ti). Alternatively, the oxide semiconductor may include a mixture of metal such as zinc (Zn), indium (In), gallium (Ga), tin (Sn), or titanium (Ti) and oxide thereof. The oxide semiconductor may include indium-tin oxide (ITO), indium-gallium-zinc oxide (IGZO), zinc oxide (ZnO), indium-zinc oxide (IZO), zinc-indium oxide (ZIO), indium oxide (InO), titanium oxide (TiO), indium-zinc-tin oxide (IZTO), or zinc-tin oxide (ZTO).

[0165] FIG. **6** merely illustrates a portion of the second semiconductor pattern, and the second semiconductor pattern may be additionally disposed in another area of the pixel PXij and other pixels PX or sensors FX. The second semiconductor pattern may include a plurality of areas distinguished depending on whether metal oxide is reduced or not. An area where metal oxide is reduced (hereinafter, referred to as the reduced area) has a higher conductivity than an area where metal oxide is not reduced (hereinafter, referred to as the non-reduced area). The reduced area may serve as an electrode or a signal line. The non-reduced area substantially may correspond to a channel part of a transistor. In other words, one portion of the second semiconductor pattern may be the channel part of a transistor, and another portion may be a first electrode or a second electrode of the transistor.

[0166] The circuit layer DP_CL may further include a portion of a semiconductor pattern of the sensor driving circuit O_SD (refer to FIG. **4**A). For convenience of description, the reset transistor ST**1** of the semiconductor pattern of the sensor driving circuit O_SD is illustrated in FIG. **6**. The first electrode STS**1**, a channel part STA**1**, and the second electrode STD**1** of the reset transistor ST**1** may be formed in the second semiconductor pattern. In an embodiment of the present disclosure, the second semiconductor pattern may include metal oxide. The first electrode STS**1** and the second electrode STD**1** include metal reduced from a metal oxide semiconductor. The first electrode STS**1** and the second electrode STD**1** may include a metal layer that has a certain thickness from the upper surface of the second semiconductor pattern and includes the reduced metal.

[0167] A fourth insulating layer **40** covers the first electrode STS**1**, the channel part STA**1**, and the second electrode STD**1** of the reset transistor ST**1**. The third electrode STG**1** of the reset transistor ST**1** is on the fourth insulating layer **40**. In this embodiment, the third electrode STG**1** may be a portion of a third gate pattern layer GAT**3** (refer to FIG. **9**E). The third electrode STG**1** of the reset transistor ST**1** overlaps the channel part STA**1** of the reset transistor ST**1**. Although one third electrode STG**1** is illustrated in this embodiment for convenience of description, the reset transistor ST**1** may include two or more third electrodes.

[0168] A fifth insulating layer **50** that covers the third electrode G**3** is on the fourth insulating layer **40**. In this embodiment, the fifth insulating layer **50** may include a silicon oxide layer and a silicon nitride layer. The fifth insulating layer **50** may include a plurality of silicon oxide layers and a plurality of silicon nitride layers alternately stacked one above another.

[0169] At least one insulating layer is additionally disposed on the fifth insulating layer **50**. In this embodiment, a sixth insulating layer **60** and a seventh insulating layer **70** may be disposed on the fifth insulating layer **50**. The sixth insulating layer **60** and the seventh insulating layer **70** may be organic layers and may have a single-layer structure or a multi-layer structure. Each of the sixth

insulating layer **60** and the seventh insulating layer **70** may be a single polyimide-based resin layer. Without being limited thereto, the sixth insulating layer **60** and the seventh insulating layer **70** may include at least one of an acrylic resin, a methacrylic resin, a polyisoprene resin, a vinyl resin, an epoxy resin, a urethane-based resin, a celluosic resin, a siloxane-based resin, a polyamide resin, or a perylene-based resin.

[0170] A first connecting electrode CNE**10** may be on the fifth insulating layer **50**. The first connecting electrode CNE**10** connects to the connecting signal line CSL through a first contact hole CH**1** penetrating the first to fifth insulating layers **10** to **50**. A second connecting electrode CNE**20** on the sixth insulating layer **60** may connect to the first connecting electrode CNE**10** through a second contact hole CH**2** penetrating the sixth insulating layer **60**. In an embodiment of the present disclosure, at least one of the fifth to seventh insulating layers **50** to **70** may be omitted, and one of the first and second connecting electrodes CNE**10** and CNE**20** may also be omitted.

[0171] A third connecting electrode CNE**11** may be on the fifth insulating layer **50**. The third connecting electrode CNE**11** connects to the second electrode STD**1** of the reset transistor ST**1** through a third contact hole CH**3** penetrating the fourth and fifth insulating layers **40** and **50**. A fourth connecting electrode CNE**21** may connect to the third connecting electrode CNE**11** through a fourth contact hole CH**4** penetrating the sixth insulating layer **60**.

[0172] The first and third connecting electrodes CNE**10** and CNE**11** may be portions of a first data metal pattern, and the second and fourth connecting electrodes CNE**20** and CNE**21** may be portions of a second data metal pattern.

[0173] The horizontal data connecting lines H_DCL (refer to FIG. **5**) may be disposed on the same layer as the first and third connecting electrodes CNE**10** and CNE**11** (that is, on the fifth insulating layer **50**). However, the present disclosure is not limited thereto. The horizontal data connecting lines H_DCL may be disposed on the same layer (that is, on the first insulating layer **10**) as the third electrode G**1** of the first transistor T**1**.

[0174] A portion (that is, a first line portion RL_P**1**) of a readout wiring RL may be on the same layer (that is, on the sixth insulating layer **60**) as the second and fourth connecting electrodes CNE**20** and CNE**21**. The readout wiring RL may be one of the readout lines RL**1** to RLh illustrated in FIG. **3**. The second and fourth connecting electrodes CNE**20** and CNE**21** and the first line portion RL_P**1** of the readout wiring RL are covered by the seventh insulating layer **70**.

[0175] A data wiring DL, the vertical data connecting lines V_DCL (refer to FIG. **5**A), a vertical reset voltage line V_VRL, the vertical connecting lines V_RL (refer to FIG. **7**A), and a portion (that is, a second line portion RL_P**2**) of the readout wiring RL may be disposed on the seventh insulating layer **70**. The data wiring DL may be one of the data lines DL**1** to DLm illustrated in FIG. **3**. The vertical reset voltage line V_VRL may be a component included in the reset voltage line VRL illustrated in FIG. **4**A.

[0176] A fifth connecting electrode CNE**30** and a sixth connecting electrode CNE**31** may be on the seventh insulating layer **70**. The fifth connecting electrode CNE**30** may connect to the second connecting electrode CNE**20** through a fifth contact hole CH**5** penetrating the seventh insulating layer **70**. The sixth connecting electrode CNE**31** may connect to the fourth connecting electrode CNE**21** through a sixth contact hole CH**6** penetrating the seventh insulating layer **70**.

[0177] The data wiring DL, the vertical data connecting lines V_DCL, the vertical connecting lines V_RL, the vertical reset voltage line V_VRL, and the second line portion RL_P**2** may be on the same layer as the fifth connecting electrode CNE**30** and the sixth connecting electrode CNE**31** but may be electrically insulated from the fifth connecting electrode CNE**30** and the sixth connecting electrode CNE**31**. An eighth insulating layer **80** may cover the data wiring DL, the vertical data connecting lines V_DCL, the vertical connecting lines V_RL, the vertical reset voltage line V_VRL, the second line portion RL_P**2**, the fifth connecting electrode CNE**30**, and the sixth connecting electrode CNE**31**.

[0178] The element layer DP_ED is on the circuit layer DP_CL. The element layer DP_ED may

include the anode electrode P_AE of the light emitting element ED (refer to FIG. **4**A) and the anode electrode O_AE of the light receiving element OPD (refer to FIG. **4**A). As illustrated in FIG. **6**, the anode electrode P_AE of the light emitting element ED may connect to the fifth connecting electrode CNE**30** through a seventh contact hole CH**7** penetrating the eighth insulating layer **80**. The anode electrode O_AE of the light receiving element OPD may connect to the sixth connecting electrode CNE**31** through an eighth contact hole CH**8** penetrating the eighth insulating layer **80**.

[0179] Although FIG. **6** illustrates a structure in which the circuit layer DP_CL includes the fifth connecting electrode CNE**30** and the sixth connecting electrode CNE**31**, the present disclosure is not limited thereto. Alternatively, the fifth connecting electrode CNE**30** and the sixth connecting electrode CNE**31** may be omitted from the circuit layer DP_CL. In this case, the anode electrode P_AE may be directly connected with the second connecting electrode CNE**20**, and the anode electrode O_AE may be directly connected with the fourth connecting electrode CNE**21**.

[0180] The element layer DP_ED further includes a pixel defining layer PDL disposed on the circuit layer DP_CL. The pixel defining layer PDL may include a light emitting opening OP**1** that correspond to the light emitting element ED and a light receiving opening OP**2** that correspond to the light receiving element OPD. The light emitting opening OP**1** exposes at least a portion of the anode electrode P_AE of the light emitting element ED. The light emitting opening OP**1** of the pixel defining layer PDL may define an emissive area PXA. For example, the plurality of pixels PX (refer to FIG. **3**) may be arranged on the plane of the display panel DP (refer to FIG. **3**) according to a certain rule for placement of openings in the pixel defining layer PDL. Areas where the plurality of pixels PX are disposed may be defined as pixel areas, and one pixel area may include an emissive area PXA and a non-emissive area NPXA adjacent to the emissive area PXA. The non-emissive area NPXA may surround the emissive area PXA.

[0181] The light receiving opening OP**2** overlaps the anode electrode O_AE of the light receiving element OPD. The light receiving opening OP**2** of the pixel defining layer PDL may define a light receiving area SA. For example, the plurality of sensors FX (refer to FIG. **3**) may be arranged on the plane of the display layer DP according to a certain rule for placement of openings in the pixel defining layer PDL. Areas where the plurality of sensors FX are disposed may be defined as sensing areas, and one sensing area may include a light receiving area SA and a non-light receiving area NSA adjacent to the light receiving area SA. The non-light receiving area NSA may surround the light receiving area SA.

[0182] An emissive layer P_EL is disposed to correspond to the light emitting opening OP**1** defined in the pixel defining layer PDL, and a photoelectric conversion layer O_RL is disposed to correspond to the light receiving opening OP**2** defined in the pixel defining layer PDL. Although the patterned emissive layer P_EL is illustrated in this embodiment, the present disclosure is not limited thereto. A common emissive layer may be commonly disposed in the plurality of pixels PX. In this case, the common emissive layer may generate white light or blue light. The common cathode electrode C_CE is commonly connected to the light emitting element ED and the light receiving element OPD. The common cathode electrode C_CE may face the anode electrode O_AE and the anode electrode P_AE. The common cathode electrode C_CE is on the emissive layer P_EL and the photoelectric conversion layer O_RL. The common cathode electrode C_CE may be commonly disposed in the plurality of pixels PX and the plurality of sensors FX.

[0183] FIG. **7**A is a plan view illustrating a portion of the display panel according to an embodiment of the present disclosure, and FIG. **7**B is an enlarged view of portion BB of FIG. **7**A. FIG. **7**C is a sectional view taken along line I-I′ illustrated in FIG. **7**B.

[0184] Each of conductive patterns and semiconductor patterns of the display panel DP may have a structure that is repeated across an area of the display panel DP according to a certain rule, and FIG. **7**A illustrates some structures of the pixel driving circuits P_PD and the sensor driving circuits O_SD that may be repeated.

[0185] Referring to FIG. **7**A, a voltage line have a mesh shape in the display area DA (refer to FIG.

5A) of the display panel DP (refer to FIG. 5A). In an embodiment of the present disclosure, the first driving voltage line VL1, the second driving voltage line VL2, and the first and second initialization voltage lines VIL and VAIL illustrated in FIG. 4A may have a mesh shape formed by connecting horizontal lines and vertical lines. Although one voltage line (that is, the second initialization voltage line VAIL) is illustrated as an example in FIG. 7A, the present disclosure is not limited thereto.

[0186] The second initialization voltage line VAIL includes a second horizontal initialization voltage line H_VAIL and a second vertical initialization voltage line V_VAIL. The second horizontal initialization voltage line H_VAIL extends in the first direction DR1, and the second vertical initialization voltage line V_VAIL extends in the second direction DR2. Accordingly, the second initialization voltage line VAIL may include a mesh shape in the display area DA of the display panel DP.

[0187] The second horizontal initialization voltage line H_VAIL and the second vertical initialization voltage line V_VAIL may be on different layers of the circuit layer DP_CL. For example, the second horizontal initialization voltage line H_VAIL may be on the fourth insulating layer **40** (refer to FIG. 6), and the second vertical initialization voltage line V_VAIL may be on the seventh insulating layer **70** (refer to FIG. 6). The second initialization voltage line VAIL may further include a second initialization connecting pattern C_VAIL for connecting the second horizontal initialization voltage line H_VAIL and the second vertical initialization voltage line V_VAIL. In an embodiment of the present disclosure, the second initialization connecting pattern C_VAIL may be on the sixth insulating layer **60** (refer to FIG. 6). The second horizontal initialization voltage line H_VAIL may be connected to the second vertical initialization voltage line V_VAIL through the second initialization connecting pattern C_VAIL.

[0188] The vertical connecting lines V_RL electrically connected with the second readout lines RL_G2 (refer to FIG. 5A) extend in the second direction DR2. The vertical connecting lines V_RL may extend parallel to the second vertical initialization voltage line V_VAIL.

[0189] The vertical connecting lines V_RL may cross at least one gate wiring. In an embodiment of the present disclosure, each of the vertical connecting lines V_RL may cross a first gate wiring SBL, a second gate wiring EML, a third gate wiring SWL, and a fourth gate wiring SCL. The first gate wiring SBL may be one of the black scan lines SBL1 to SBLn illustrated in FIG. 3, and the second gate wiring EML may be one of the emission control lines EML1 to EMLn illustrated in FIG. 3. The third gate wiring SWL may be one of the write scan lines SWL1 to SWLn illustrated in FIG. 3, and the fourth gate wiring SCL may be one of the compensation scan lines SCL1 to SCLn illustrated in FIG. 3.

[0190] To decrease the third coupling capacitance Ccp3, the display panel DP includes the shielding pattern disposed in the area where each of the vertical connecting lines V_RL crosses at least one of the first to fourth gate wirings SBL, EML, SWL, and SCL. In an embodiment of the present disclosure, the shielding pattern may include a first shielding pattern S_SP1 extending from the second horizontal initialization voltage line H_VAIL. In an embodiment shown in FIG. 7B, the first shielding pattern S_SP1 may include a first shielding portion SP1_1 parallel to the first direction DR1 and a second shielding portion SP1_2 parallel to the second direction DR2. The first shielding portion SP1_1 of the first shielding pattern S_SP1 overlaps the vertical connecting lines V_RL, the first gate wiring SBL, and the second gate wiring EML when viewed from above the plane and is disposed between the vertical connecting lines V_RL and the first and second gate wirings SBL and EML in the normal direction perpendicular to the plane.

[0191] The first shielding pattern S_SP1 may have the same potential (that is, the second initialization voltage Vaint) as the second horizontal initialization voltage line H_VAIL. Since the second initialization voltage Vaint is a DC voltage, the first shielding pattern S_SP1 may have a constant potential.

[0192] Referring to FIG. 7C, the first and second gate wirings SBL and EML are disposed on the

first insulating layer **10**. The second to fourth insulating layers **20**, **30**, and **40** are sequentially stacked on the first and second gate wirings SBL and EML. The second horizontal initialization voltage line H_VAIL and the first shielding pattern S_SP**1** are disposed on the fourth insulating layer **40**. The first shielding pattern S_SP**1** may face the first and second gate wirings SBL and EML with the second to fourth insulating layers **20**, **30**, and **40** therebetween.

[0193] The fifth to seventh insulating layers **50**, **60**, and **70** are sequentially stacked on the second horizontal initialization voltage line H_VAIL and the first shielding pattern S_SP**1**. The vertical connecting lines V_RL are on the seventh insulating layer **70**. The vertical connecting lines V_RL may face the first shielding pattern S_SP**1** with the fifth to seventh insulating layers **50**, **60**, and **70** therebetween. That is, the first shielding pattern S_SP**1** may be between the vertical connecting lines V_RL and the first and second gate wirings SBL and EML in the third direction DR**3**. The third coupling capacitance formed between the vertical connecting lines V_RL and the first and second gate wirings SBL and EML may be decreased by the first shielding pattern S_SP**1** having the constant potential, and thus a deviation in coupling capacitance between the first and second readout lines RL_G**1** and RL_G**2** may be decreased. Accordingly, deterioration in the sensing accuracy of the sensor FX (refer to FIG. **3**) due to a deviation in coupling capacitance may be prevented.

[0194] FIG. **8**A is a plan view illustrating a portion of the display panel according to an embodiment of the present disclosure, and FIG. **8**B is an enlarged view of portion CC of FIG. **8**A. FIG. **8**C is a sectional view taken along line II-II′ illustrated in FIG. **8**B.

[0195] Referring to FIG. **8**A, the first initialization voltage line VIL includes a first horizontal initialization voltage line H_VIL and a first vertical initialization voltage line V_VIL. The first horizontal initialization voltage line H_VIL extends in the first direction DR**1**, and the first vertical initialization voltage line V_VIL extends in the second direction DR**2**. Accordingly, the first initialization voltage line VIL may have a mesh shape in the display area DA (refer to FIG. **3**) of the display panel DP (refer to FIG. **3**).

[0196] The first horizontal initialization voltage line H_VIL and the first vertical initialization voltage line V_VIL may be on different layers of the circuit layer DP_CL (refer to FIG. **6**). For example, the first horizontal initialization voltage line H_VIL may be on the fifth insulating layer **50** (refer to FIG. **6**), and the first vertical initialization voltage line V_VIL may be on the seventh insulating layer **70** (refer to FIG. **6**). The first initialization voltage line VIL may further include a first initialization connecting pattern C_VIL for connecting the first horizontal initialization voltage line H_VIL and the first vertical initialization voltage line V_VIL. In an embodiment of the present disclosure, the first initialization connecting pattern C_VIL may be on the sixth insulating layer **60** (refer to FIG. **6**). The first horizontal initialization voltage line H_VIL may be connected to the first vertical initialization voltage line V_VIL through the first initialization connecting pattern C_VIL.

[0197] In an embodiment of the present disclosure, the shielding pattern may further include a second shielding pattern S_SP**2** extending from the first horizontal initialization voltage line H_VIL in the direction opposite to the second direction DR**2**. Accordingly, the second shielding pattern S_SP**2** may have the same potential (that is, the first initialization voltage Vint) as the first horizontal initialization voltage line H_VIL. Since the first initialization voltage Vint is a DC voltage, the second shielding pattern S_SP**2** may have a constant potential.

[0198] The second shielding pattern S_SP**2**, as shown in FIG. **8**B, overlaps the vertical connecting lines V_RL, the third gate wiring SWL, and the fourth gate wiring SCL when viewed from above the plane and is between the vertical connecting lines V_RL and the third and fourth gate wirings SWL and SCL in the normal direction perpendicular to the plane.

[0199] Referring to FIG. **8**C, the third gate wiring SWL is on the first insulating layer **10**. The fourth gate wiring SCL includes a fourth-first gate wiring G**2**_SCL disposed on the second insulating layer **20** and a fourth-second gate wiring G**3**_SCL on the fourth insulating layer **40**.

[0200] The third and fourth insulating layers **30** and **40** are sequentially stacked on the fourth-first

gate wiring G**2**_SCL, and the fifth insulating layer **50** is on the fourth-second gate wiring G**3**_SCL. The first horizontal initialization voltage line H_VIL and the second shielding pattern S_SP**2** are on the fifth insulating layer **50**. The second shielding pattern S_SP**2** may face the third gate wiring SWL and the fourth-second gate wiring G**3**_SCL with the fifth insulating layer **50** therebetween.
[0201] The sixth and seventh insulating layers **60** and **70** are sequentially stacked on the first horizontal initialization voltage line H_VIL and the second shielding pattern S_SP**2**. The vertical connecting lines V_RL are on the seventh insulating layer **70**. The vertical connecting lines V_RL may face the second shielding pattern S_SP**2** with the sixth and seventh insulating layers **60** and **70** therebetween. That is, the second shielding pattern S_SP**2** may be between the vertical connecting lines V_RL and the third gate wiring SWL and the fourth-second gate wiring G**3**_SCL in the third direction DR**3**.
[0202] In an embodiment of the present disclosure, the first horizontal initialization voltage line H_VIL may overlap a fifth gate wiring SIL when viewed from above the plane. The fifth gate wiring SIL includes a fifth-first gate wiring G**2**_SIL on the second insulating layer **20** and a fifth-second gate wiring G**3**_SIL on the fourth insulating layer **40**. That is, the first horizontal initialization voltage line H_VIL may be between the vertical connecting lines V_RL and the fifth-second gate wiring G**3**_SIL in the third direction DR**3**.
[0203] The third coupling capacitance Ccp**3** formed between the vertical connecting lines V_RL and the third gate wiring SWL and the fourth-second gate wiring G**3**_SCL may be decreased by the second shielding pattern S_SP**2** having the constant potential, and thus a deviation in coupling capacitance between the first and second readout lines RL_G**1** and RL_G**2** may be decreased. Accordingly, deterioration in the sensing accuracy of the sensor FX (refer to FIG. **3**) due to a deviation in coupling capacitance may be prevented.
[0204] FIGS. **9**A to **9**H are plan views illustrating an arrangement order of circuit layers according to an embodiment of the present disclosure.
[0205] Referring to FIGS. **9**A to **9**H, each of conductive patterns and semiconductor patterns may have a structure that is repeated across the area of the circuit layer DP_CL according to a certain rule when viewed from above the plane. FIGS. **9**A to **9**H show some of the pixel driving circuits P_PD and some of the sensor driving circuits O_SD.
[0206] Referring to FIG. **9**A, a first semiconductor pattern layer ACT**1** may be on the buffer layer BFL. The first semiconductor pattern layer ACT**1** may include a silicon semiconductor. For example, the silicon semiconductor may include amorphous silicon or polycrystalline silicon. For example, the first semiconductor pattern layer ACT**1** may include low-temperature polycrystalline silicon (LTPS).
[0207] The first semiconductor pattern layer ACT**1** includes a first semiconductor pattern P_ACT**1** included in the pixel driving circuit P_PD and a second semiconductor pattern S_ACT**1** included in the sensor driving circuit O_SD.
[0208] Referring to FIG. **9**B, the first gate pattern layer GAT**1** may be on the first insulating layer **10**. The first gate pattern layer GAT**1** may include metal, an alloy, conductive metal oxide, or a transparent conductive material. For example, the first gate pattern layer GAT**1** may include silver (Ag), an alloy containing silver, molybdenum (Mo), an alloy containing molybdenum, aluminum (Al), an alloy containing aluminum, aluminum nitride (AlN), tungsten (W), tungsten nitride (WN), copper (Cu), indium tin oxide (ITO), or indium zinc oxide (IZO), but is not particularly limited thereto.
[0209] The first gate pattern layer GAT**1** may include the first gate wiring SBL, the second gate wiring EML, the third gate wiring SWL, a first gate electrode GE**1**, and a second gate electrode GE**2**.
[0210] Each of the first, second, and third gate wirings SBL, EML, and SWL may extend in the first direction DR**1**. The first gate wiring SBL may correspond to the j-th black scan line SBLj of FIG. **4**A. For example, the j-th black scan signal SBj (refer to FIG. **4**A) may be provided to the first

gate wiring SBL. The first gate wiring SBL together with the first semiconductor pattern P_ACT**1** may constitute the seventh transistor T**7** of FIG. **4**A.
[0211] The second gate wiring EML corresponds to the j-th emission control line EMLj of FIG. **4**A. For example, the j-th emission control signal EMj (refer to FIG. **4**A) may be provided to the second gate wiring EML. The second gate wiring EML together with the first semiconductor pattern P_ACT**1** may constitute the fifth and sixth transistors T**5** and T**6** of FIG. **4**A.
[0212] The third gate wiring SWL corresponds to the j-th write scan line SWLj of FIG. **4**A. For example, the j-th write scan signal SWj (refer to FIG. **4**A) may be provided to the third gate wiring SWL. The third gate wiring SWL together with the first semiconductor pattern P_ACT**1** may constitute the second transistor T**2** of FIG. **4**A, and the third gate wiring SWL together with the second semiconductor pattern S_ACT**1** may constitute the output transistor ST**3** of FIG. **4**A.
[0213] Each of the first and second gate electrodes GE**1** and GE**2** may be an island shaped region. The first gate electrode GE**1** together with the first semiconductor pattern P_ACT**1** may constitute the first transistor T**1** of FIG. **4**A. The first gate electrode GE**1** may correspond to the third electrode G**1** of the first transistor T**1** illustrated in FIG. **6**. The second gate electrode GE**2** together with the second semiconductor pattern S_ACT**1** may constitute the amplifying transistor ST**2** of FIG. **4**A.
[0214] Referring to FIG. **9**C, the second insulating layer **20** may be on the first insulating layer **10** and may cover the first gate pattern layer GAT**1**. The second gate pattern layer GAT**2** may be on the second insulating layer **20**. The second gate pattern layer GAT**2** may include metal, an alloy, conductive metal oxide, or a transparent conductive material.
[0215] The second gate pattern layer GAT**2** may include the fourth-first gate wiring G**2**_SCL, the fifth-first gate wiring G**2**_SIL, a sixth-first gate wiring G**2**_SRL, and a capacitor electrode CSE.
[0216] The fourth-first gate wiring G**2**_SCL, the fifth-first gate wiring G**2**_SIL, and the sixth-first gate wiring G**2**_SRL may extend in the first direction DR**1**. The sixth-first gate wiring G**2**_SRL corresponds to (or is included in) the reset control line SRL (refer to FIG. **4**A). The fourth-first gate wiring G**2**_SCL may correspond to (or may be included in) the j-th compensation scan line SCLj (refer to FIG. **4**A). The fifth-first gate wiring G**2**_SIL may correspond to (or may be included in) the j-th initialization scan line SILj (refer to FIG. **4**A).
[0217] The capacitor electrode CSE may overlap the first gate electrode GE**1** and may be an island shaped region. For example, the capacitor electrode CSE together with the first gate electrode GE**1** may constitute the capacitor Cst (refer to FIG. **4**A). The first gate electrode GE**1** may correspond to the upper electrode UE illustrated in FIG. **6**. An opening CSE_OP penetrating the capacitor electrode CSE may be formed in the capacitor electrode CSE, and the first gate electrode GE**1** may be partially exposed through the opening CSE_OP.
[0218] Referring to FIG. **9**D, the third insulating layer **30** may be on the second insulating layer **20** and may cover the second gate pattern layer GAT**2**. A second semiconductor pattern layer ACT**2** may be on the third insulating layer **30**. The second semiconductor pattern layer ACT**2** may include an oxide semiconductor. The second semiconductor pattern layer ACT**2** may be in a layer different from the first semiconductor pattern layer ACT**1** and may not overlap the first semiconductor pattern layer ACT**1**.
[0219] The second semiconductor pattern layer ACT**2** includes a third semiconductor pattern P_ACT**2** included in the pixel driving circuit P_PD and a fourth semiconductor pattern S_ACT**2** included in the sensor driving circuit O_SD.
[0220] Referring to FIG. **9**E, the fourth insulating layer **40** may be on the third insulating layer **30** and may cover the second semiconductor pattern layer ACT**2**. The third gate pattern layer GAT**3** may be on the fourth insulating layer **40**. The third gate pattern layer GAT**3** may include metal, an alloy, conductive metal oxide, or a transparent conductive material.
[0221] The third gate pattern layer GAT**3** may include the fourth-second gate wiring G**3**_SCL, the fifth-second gate wiring G**3**_SIL, a sixth-second gate wiring G**3**_SRL, a second-first horizontal

initialization voltage line H_VAIL**1**, and a second-second horizontal initialization voltage line H_VAIL**2**. The fourth-second gate wiring G**3**_SCL, the fifth-second gate wiring G**3**_SIL, the sixth-second gate wiring G**3**_SRL, the second-first horizontal initialization voltage line H_VAIL**1**, and the second-second horizontal initialization voltage line H_VAIL**2** extend in the first direction DR**1**.
[0222] The fifth-second gate wiring G**3**_SIL may overlap the fourth-first gate wiring G**2**_SCL and the third semiconductor pattern P_ACT**2**. In some embodiments, the fourth-second gate wiring G**3**_SCL may make contact with the fourth-first gate wiring G**2**_SCL through a contact portion. Accordingly, the j-th compensation scan signal SCj applied to the fourth-first gate wiring G**2**_SCL may be provided to the fourth-second gate wiring G**3**_SCL. The fourth-first gate wiring G**2**_SCL, the third semiconductor pattern P_ACT**2**, and the fourth-second gate wiring G**3**_SCL may constitute the third transistor T**3** of FIG. **4**A.
[0223] The fifth-second gate wiring G**3**_SIL may overlap the fifth-first gate wiring G**2**_SIL and the third semiconductor pattern P_ACT**2**. The fifth-second gate wiring G**3**_SIL may be electrically connected with the fifth-first gate wiring G**2**_SIL. The j-th initialization scan signal SIj may be provided to the fifth-second gate wiring G**3**_SIL through the fifth-first gate wiring G**2**_SIL. The fifth-first gate wiring G**2**_SIL, the third semiconductor pattern P_ACT**2**, and the fifth-second gate wiring G**3**_SIL may constitute the fourth transistor T**4** of FIG. **4**A.
[0224] The sixth-second gate wiring G**3**_SRL may overlap the fourth semiconductor pattern S_ACT**2**. The sixth-second gate wiring G**3**_SRL together with the fourth semiconductor pattern S_ACT may constitute the reset transistor ST**1** of FIG. **4**A**2**. The sixth-second gate wiring G**3**_SRL may be electrically connected with the sixth-first gate wiring G**2**_SRL illustrated in FIG. **9**C.
[0225] The second-first horizontal initialization voltage line H_VAIL**1** and the second-second horizontal initialization voltage line H_VAIL**2** may be spaced apart from each other in the second direction DR**2**. In an embodiment of the present disclosure, the second initialization voltage line VAIL (refer to FIG. **4**A) may include a second-first initialization voltage line and a second-second initialization voltage line. The second-first initialization voltage line is connected to at least one pixel (in particular, a first light emitting element of a first pixel) among the plurality of pixels PX illustrated in FIG. **3**, and the second-second initialization voltage line is connected to another pixel (e.g., second and third light emitting elements of second and third pixels) among the plurality of pixels PX. In an embodiment of the present disclosure, the first pixel includes the first light emitting element that outputs light of a first color (e.g., red light), the second pixel includes the second light emitting element that outputs light of a second color (e.g., green light), and the third pixel includes the third light emitting element that outputs light of a third color (e.g., blue light).
[0226] Here, the second-first horizontal initialization voltage line H_VAIL**1** may be a component included in the second-first initialization voltage line, and the second-second horizontal initialization voltage line H_VAIL**2** may be a component included in the second-second initialization voltage line. The second-first horizontal initialization voltage line H_VAIL**1** applies a second-first horizontal initialization voltage to the first pixel as the second initialization voltage Vaint (refer to FIG. **4**A), and the second-second horizontal initialization voltage line H_VAIL**2** applies a second-second horizontal initialization voltage to the second and third pixels as the second initialization voltage Vaint. The second-second horizontal initialization voltage may have a voltage level different from that of the second-first horizontal initialization voltage.
[0227] The third gate pattern layer GAT**3** further includes the first shielding pattern S_SP**1**. The first shielding pattern S_SP**1** may extend from the second-first horizontal initialization voltage line H_VAIL**1**. However, the present disclosure is not limited thereto. For example, the first shielding pattern S_SP**1** may be provided on the second-second horizontal initialization voltage line H_VAIL**2**, or the first shielding pattern S_SP**1** may be provided on each of the second-first horizontal initialization voltage line H_VAIL**1** and the second-second horizontal initialization voltage line H_VAIL**2**.
[0228] Referring to FIG. **9**F, the fifth insulating layer **50** may be on the fourth insulating layer **40**

and may cover at least a portion of the third gate pattern layer GAT**3**. A first data pattern layer SD**1** may be on the fifth insulating layer **50**. The first data pattern layer SD**1** may include, for example, metal, an alloy, conductive metal oxide, or a transparent conductive material. Hereinafter, for convenience of description and illustration, FIG. **9**F shows only some of the components included in the first data pattern layer SD**1**.

[0229] The first data pattern layer SD**1** may include a horizontal reset voltage line H_VRL, the bias voltage line VBL, the first horizontal initialization voltage line H_VIL, and a plurality of first connecting electrode patterns C_CNE**1**.

[0230] The horizontal reset voltage line H_VRL, the bias voltage line VBL, and the first horizontal initialization voltage line H_VIL may extend in the first direction DR**1**. The horizontal reset voltage line H_VRL, the bias voltage line VBL, and the first horizontal initialization voltage line H_VIL may be spaced apart from one another in the second direction DR**2**.

[0231] The horizontal reset voltage line H_VRL may be a component included in the reset voltage line VRL of FIG. **4**A. The reset voltage Vrst (refer to FIG. **4**A) may be provided to the horizontal reset voltage line H_VRL. The horizontal reset voltage line H_VRL may be electrically connected with the reset transistor ST**1**. The reset transistor ST**1** may receive the reset voltage Vrst through the horizontal reset voltage line H_VRL. The bias voltage line VBL may correspond to the bias voltage line VBL of FIG. **4**A. The bias voltage Vbias (refer to FIG. **4**A) may be provided to the bias voltage line VBL. The bias voltage line VBL may be connected with the eighth transistor T**8** through a contact portion. The eighth transistor T**8** may receive the bias voltage Vbias through the bias voltage line VBL.

[0232] The first horizontal initialization voltage line H_VIL may be included in the first initialization voltage line VIL of FIG. **4**A. The first initialization voltage Vint (refer to FIG. **4**A) may be provided to the first horizontal initialization voltage line H_VIL. The first horizontal initialization voltage line H_VIL may be connected with the fourth transistor T**4** through a contact portion. The fourth transistor T**4** may receive the first initialization voltage Vint through the first horizontal initialization voltage line H_VIL.

[0233] The plurality of first connecting electrode patterns C_CNE**1** may make contact with one of the first to fourth semiconductor patterns P_ACT**1**, S_ACT**1**, P_ACT**2**, and S_ACT**2**. The plurality of first connecting electrode patterns C_CNE**1** may electrically connect one of the first to fourth semiconductor patterns P_ACT**1**, S_ACT**1**, P_ACT**2**, and S_ACT**2** to other wiring or lines. The plurality of first connecting electrode patterns C_CNE**1** may be connected with one of the first to fourth semiconductor patterns P_ACT**1**, S_ACT**1**, P_ACT**2**, and S_ACT**2** through a contact portion. The plurality of first connecting electrode patterns C_CNE**1** may include the first and third connecting electrodes CNE**10** and CNE**11** illustrated in FIG. **6**.

[0234] The first data pattern layer SD**1** may further include the second shielding pattern S_SP**2**. In an embodiment of the present disclosure, the second shielding pattern S_SP**2** may extend from the first horizontal initialization voltage line H_VIL.

[0235] The first data pattern layer SD**1** may further include a horizontal data connecting wiring D**1**_HCL. The horizontal data connecting wiring D**1**_HCL may extend in the first direction DR**1**. In an embodiment of the present disclosure, the horizontal data connecting wiring D**1**_HCL may be a component included in the horizontal data connecting lines H_DCL illustrated in FIG. **5**A.

[0236] Referring to FIG. **9**G, the sixth insulating layer **60** may be on the fifth insulating layer **50** and may cover at least a portion of the first data pattern layer SD**1**. A second data pattern layer SD**2** may be on the sixth insulating layer **60**. The second data pattern layer SD**2** may include, for example, metal, an alloy, conductive metal oxide, or a transparent conductive material.

[0237] The second data pattern layer SD**2** includes the first driving voltage line VL**1**, a shielding electrode wiring RSE, the first line portion RL_P**1** of the readout wiring RL (refer to FIG. **6**), and a plurality of connecting patterns.

[0238] The first driving voltage line VL**1** may overlap the pixel driving circuit P_PD. The first

driving voltage line VL**1** may correspond to the first driving voltage line VL**1** of FIG. **4**A. The first driving voltage ELVDD (refer to FIG. **4**A) may be provided to the first driving voltage line VL**1**. The first driving voltage line VL**1** may be disposed in a mesh shape in the display area DA (refer to FIG. **3**) of the display panel DP. The first driving voltage line VL**1** may be connected, through a contact portion, with the fifth transistor T**5** and the capacitor Cst, which are illustrated in FIG. **4**A.
[0239] The shielding electrode wiring RSE may be connected with the horizontal reset voltage line H_VRL illustrated in FIG. **9**F and may receive the reset voltage Vrst (refer to FIG. **4**A) through the horizontal reset voltage line H_VRL. When viewed from above the plane, the shielding electrode wiring RSE may be disposed between the readout wiring RL and the data wiring DL (refer to FIG. **9**H). Accordingly, the shielding electrode wiring RSE may perform a shielding function such that a detection signal output from the readout wiring RL does not couple to a data signal.
[0240] The first line portion RL_P**1** and the vertical reset voltage line V_VRL extend in the second direction DR**2** and are spaced apart from each other in the first direction DR**1**. The readout wiring RL may correspond to the readout lines RL**1** to RLh illustrated in FIG. **3**. The readout wiring RL may be connected to the sensor driving circuit O_SD illustrated in FIG. **4**A (in particular, the output transistor ST**3**).
[0241] The plurality of connecting patterns may include the second initialization connecting pattern C_VAIL and the first initialization connecting pattern C_VIL (refer to FIG. **8**A).
[0242] The second data pattern layer SD**2** may further include a plurality of second connecting electrode patterns C_CNE**2**. The plurality of second connecting electrode patterns C_CNE**2** may include the second and fourth connecting electrodes CNE**20** and CNE**21** illustrated in FIG. **6**.
[0243] Referring to FIG. **9**H, the seventh insulating layer **70** may be on the sixth insulating layer **60** and may cover at least a portion of the second data pattern layer SD**2**. A third data pattern layer SD**3** may be disposed on the seventh insulating layer **70**. The third data pattern layer SD**3** may include, for example, metal, an alloy, conductive metal oxide, or a transparent conductive material.
[0244] The third data pattern layer SD**3** may include the data wiring DL, a vertical data connecting wiring D**3**_DCL, a second-first vertical initialization voltage line V_VAIL**1**, the vertical connecting line V_RL, vertical reset voltage lines V_VRL**1** and V_VRL**2**, and a plurality of third connecting electrode patterns C_CNE**3**.
[0245] The data wiring DL, the vertical data connecting wiring D**3**_DCL, the second-first vertical initialization voltage line V_VAIL**1**, and the vertical connecting line V_RL may extend in the second direction DR**2**. The data wiring DL, the vertical data connecting wiring D**3**_DCL, the second-first vertical initialization voltage line V_VAIL**1**, and the vertical connecting line V_RL may be spaced apart from one another in the first direction DR**1**.
[0246] The data wiring DL may correspond to the data lines DL**1** to DLm illustrated in FIG. **3**. The data wiring DL may be connected to the pixel driving circuit P_PD illustrated in FIG. **4**A (in particular, the second transistor T**2**). The vertical data connecting wiring D**3**_DCL may correspond to the vertical data connecting line V_DCL illustrated in FIG. **5**A. The vertical data connecting wiring D**3**_DCL may be electrically connected with the horizontal data connecting wiring D**1**_HCL illustrated in FIG. **9**F.
[0247] The second-first vertical initialization voltage line V_VAIL**1** is electrically connected to the second-first horizontal initialization voltage line H_VAIL**1** illustrated in FIG. **9**E. The third data pattern layer SD**3** may further include a second-second vertical initialization voltage line electrically connected to the second-second horizontal initialization voltage line H_VAIL**2**. The third data pattern layer SD**3** may further include the first vertical initialization voltage line V_VIL (refer to FIG. **8**A) electrically connected with the first horizontal initialization voltage line H_VIL illustrated in FIG. **9**F.
[0248] The vertical reset voltage lines V_VRL**1** and V_VRL**2** may be components included in the reset voltage line VRL of FIG. **4**A. The vertical reset voltage lines V_VRL**1** and V_VRL**2** may be connected with the horizontal reset voltage line H_VRL illustrated in FIG. **9**F. The reset voltage

line VRL may have a mesh shape by the coupling of the vertical reset voltage lines V_VRL**1** and V_VRL**2** and the horizontal reset voltage line H_VRL.
[0249] The plurality of third connecting electrode patterns C_CNE**3** may include the fifth connecting electrode CNE**30** and the sixth connecting electrode CNE**31** illustrated in FIG. **6**.
[0250] FIG. **10**A is a plan view illustrating a portion of a display panel according to an embodiment of the present disclosure, and FIG. **10**B is an enlarged view of portion EE of FIG. **10**A. FIG. **11**A is a plan view illustrating a portion of the display panel according to an embodiment of the present disclosure, and FIG. **11**B is an enlarged view of portion FF of FIG. **11**A.
[0251] Referring to FIGS. **10**A and **10**B, the second initialization voltage line VAIL includes the second horizontal initialization voltage line H_VAIL and the second vertical initialization voltage line V_VAIL. The second horizontal initialization voltage line H_VAIL extends in the first direction DR**1**, and the second vertical initialization voltage line V_VAIL extends in the second direction DR**2**. Accordingly, the second initialization voltage line VAIL may have in a mesh shape in the display area DA of the display panel DP.
[0252] Vertical connecting lines V_RLa electrically connected with the second readout lines RL_G**2** (refer to FIG. **5**A) extend in the second direction DR**2**. The vertical connecting lines V_RLa may extend parallel to the vertical data connecting wiring D**3**_DCL.
[0253] The vertical connecting lines V_RLa may cross at least one gate wiring. In an embodiment of the present disclosure, each of the vertical connecting lines V_RLa may cross the first gate wiring SBL, the second gate wiring EML, the third gate wiring SWL, and the fourth gate wiring SCL. The first gate wiring SBL may be one of the black scan lines SBL**1** to SBLn illustrated in FIG. **3**, and the second gate wiring EML may be one of the emission control lines EML**1** to EMLn illustrated in FIG. **3**. The third gate wiring SWL may be one of the write scan lines SWL**1** to SWLn illustrated in FIG. **3**, and the fourth gate wiring SCL may be one of the compensation scan lines SCL**1** to SCLn illustrated in FIG. **3**.
[0254] To decrease the third coupling capacitance Ccp**3** (refer to FIG. **5**B), the display panel DP includes a shielding pattern in the area where each of the vertical connecting lines V_RLa crosses at least one of the first to fourth gate wirings SBL, EML, SWL, and SCL. In an embodiment of the present disclosure, the shielding pattern may include a first shielding pattern S_SP**1***a* extending from the second horizontal initialization voltage line H_VAIL in the second direction DR**2**. Accordingly, the first shielding pattern S_SP**1***a* may have the same potential (that is, the second initialization voltage Vaint) as the second horizontal initialization voltage line H_VAIL. Since the second initialization voltage Vaint is a DC voltage, the first shielding pattern S_SP**1***a* may have a constant potential.
[0255] The first shielding pattern S_SP**1***a* overlaps the vertical connecting lines V_RLa, the first gate wiring SBL, and the second gate wiring EML when viewed from above the plane and is between the vertical connecting lines V_RLa and the first and second gate wirings SBL and EML in the normal direction perpendicular to the plane.
[0256] Referring to FIGS. **11**A and **11**B, the first initialization voltage line VIL includes the first horizontal initialization voltage line H_VIL and the first vertical initialization voltage line V_VIL. The first horizontal initialization voltage line H_VIL extends in the first direction DR**1**, and the first vertical initialization voltage line V_VIL extends in the second direction DR**2**.
[0257] In an embodiment of the present disclosure, the shielding pattern may further include a second shielding pattern S_SP**2***a* extending from the first horizontal initialization voltage line H_VIL in the direction opposite to the second direction DR**2**. Accordingly, the second shielding pattern S_SP**2***a* may have the same potential (that is, the first initialization voltage Vint) as the first horizontal initialization voltage line H_VIL. Since the first initialization voltage Vint is a DC voltage, the second shielding pattern S_SP**2***a* may receive the DC voltage.
[0258] The second shielding pattern S_SP**2***a* overlaps the vertical connecting lines V_RLa, the third gate wiring SWL, and the fourth gate wiring SCL when viewed from above the plane and is

disposed between the vertical connecting lines V_RLa and the third and fourth gate wirings SWL and SCL in the normal direction perpendicular to the plane.

[0259] In FIGS. **10**B and **11**B, the first and second shielding patterns S_SP**1***a* and S_SP**2***a* are illustrated to have a bar shape. However, the present disclosure is not limited thereto, and the first and second shielding patterns S_SP**1***a* and S_SP**2***a* may have a structure extending in various shapes to overlap the gate wirings SBL, EML, SWL, and SCL depending on the design of the pixel PX and the sensor FX.

[0260] FIGS. **12**A and **12**B are sectional views illustrating light emitting elements and light receiving elements of a display panel according to an embodiment of the present disclosure.

[0261] Referring to FIGS. **12**A and **12**B, a first electrode layer is on the circuit layer DP_CL. The pixel defining layer PDL is formed on the first electrode layer. The first electrode layer may include red, green, and blue anode electrodes R_AE, G_AE, and B_AE. First to third light emitting openings OP**1_1**, OP**1_2**, and OP**1_3** of the pixel defining layer PDL expose at least portions of the red, green, and blue anode electrodes R_AE, G_AE, and B_AE, respectively. In an embodiment of the present disclosure, the pixel defining layer PDL may include a black material. The pixel defining layer PDL may, for example, include a black organic dye/pigment, such as carbon black, aniline black, or the like. The pixel defining layer PDL may be formed by mixing a blue organic material and a black organic material. The pixel defining layer PDL may further include a liquid-repellent organic material.

[0262] As illustrated in FIG. **12**A, the display panel DP may include first to third emissive areas PXA-R, PXA-G, and PXA-B and first to third non-emissive areas NPXA-R, NPXA-G, and NPXA-B adjacent to the first to third emissive areas PXA-R, PXA-G, and PXA-B. The non-emissive areas NPXA-R, NPXA-G, and NPXA-B may surround the corresponding emissive areas PXA-R, PXA-G, and PXA-B, respectively. In this embodiment, the first emissive area PXA-R is defined to correspond to a portion of the red anode electrode R_AE exposed by the first light emitting opening OP**1_1**. The second emissive area PXA-G is defined to correspond to a portion of the green anode electrode G_AE exposed by the second light emitting opening OP**1_2**. The third emissive area PXA-B is defined to correspond to a portion of the blue anode electrode B_AE exposed by the third light emitting opening OP**1_3**. A non-pixel area NPA may be defined between the first to third non-emissive areas NPXA-R, NPXA-G, and NPXA-B.

[0263] An emissive layer may be disposed on the first electrode layer. The emissive layer may include red, green, and blue light emitting layers R_EL, G_EL, and B_EL. The red, green, and blue light emitting layers R_EL, G_EL, and B_EL may be in areas respectively corresponding to the first to third light emitting openings OP**1_1**, OP**1_2**, and OP**1_3**. The red, green, and blue light emitting layers R_EL, G_EL, and B_EL may be formed to be separated from one another. Each of the red, green, and blue light emitting layers R_EL, G_EL, and B_EL may include an organic material and/or an inorganic material. The red, green, and blue light emitting layers R_EL, G_EL, and B_EL may generate light of certain colors. For example, the red light emitting layer R_EL may generate red light, the green light emitting layer G_EL may generate green light, and the blue light emitting layer B_EL may generate blue light.

[0264] Although the patterned red, green, and blue light emitting layers R_EL, G_EL, and B_EL are illustrated in this embodiment, one light emitting layer may be commonly disposed in the first to third emissive areas PXA_R, PXA_G, and PXA_B. In this case, the light emitting layer may generate white light or blue light. In addition, the light emitting layer may have a multi-layer structure, e.g., a tandem structure.

[0265] Each of the red, green, and blue light emitting layers R_EL, G_EL, and B_EL may include a low molecular weight organic material or a high molecular weight organic material as a luminescent material. Alternatively, each of the red, green, and blue light emitting layers R_EL, G_EL, and B_EL may include a quantum-dot material as a luminescent material. A core of a quantum dot may be selected from Group II-VI compounds, Group III-V compounds, Group IV-VI

compounds, Group IV elements, Group IV compounds, and combinations thereof.
[0266] A second electrode layer is on the red, green, and blue light emitting layers R_EL, G_EL, and B_EL. The second electrode layer may include red, green, and blue cathode electrodes R_CE, G_CE, and B_CE. The red, green, and blue cathode electrodes R_CE, G_CE, and B_CE may be electrically connected with one another. In an embodiment of the present disclosure, the red, green, and blue cathode electrodes R_CE, G_CE, and B_CE may have a one-body shape. In this case, the red, green, and blue cathode electrodes R_CE, G_CE, and B_CE may be commonly disposed in the first to third emissive areas PXA-R, PXA-G, and PXA-B, the first to third non-emissive areas NPXA-R, NPXA-G, and NPXA-B, and the non-pixel area NPA.
[0267] The element layer DP_ED may further include a light receiving element OPD. The light receiving element OPD may be a photo diode. The pixel defining layer PDL may further include a light receiving opening OP**2** corresponding to the light receiving element OPD.
[0268] The light receiving element OPD may include a sensing anode electrode O_AE, a photoelectric conversion layer O_RL, and a sensing cathode electrode O_CE. The sensing anode electrode O_AE may be part of the first electrode layer. That is, the sensing anode electrode O_AE may be on the circuit layer DP_CL and may be simultaneously formed with the red, green, and blue anode electrodes R_AE, G_AE, and B_AE through the same process.
[0269] The light receiving opening OP**2** of the pixel defining layer PDL exposes at least a portion of the sensing anode electrode O_AE. The photoelectric conversion layer O_RL is on the sensing anode electrode O_AE exposed by the light receiving opening OP**2**. The photoelectric conversion layer O_RL may include an organic photo sensing material. The sensing cathode electrode O_CE may be on the photoelectric conversion layer O_RL. The sensing cathode electrode O_CE may be simultaneously formed with the red, green, and blue cathode electrodes R_CE, G_CE, and B_CE through the same process. In an embodiment of the present disclosure, the sensing cathode electrode O_CE may have a one-body shape with the red, green, and blue cathode electrodes R_CE, G_CE, and B_CE to form the common cathode electrode C_CE (refer to FIG. **6**).
[0270] The encapsulation layer TFE is on the element layer DP_ED. The encapsulation layer TFE includes at least an inorganic layer or an organic layer. In an embodiment of the present disclosure, the encapsulation layer TFE may include two inorganic layers and an organic layer therebetween. In an embodiment of the present disclosure, the encapsulation layer TFE may include a plurality of inorganic layers and a plurality of organic layers alternately stacked one above another.
[0271] The inorganic layers protect the red, green, and blue light emitting elements ED_R, ED_G, and ED_B and the light receiving element OPD from moisture/oxygen, and the organic layers protect the red, green, and blue light emitting elements ED_R, ED_G, and ED_B and the light receiving element OPD from foreign matter such as dust particles. The inorganic layers may include a silicon nitride layer, a silicon oxynitride layer, a silicon oxide layer, a titanium oxide layer, or an aluminum oxide layer but are not particularly limited thereto. The organic layers may include an acrylic organic layer but are not particularly limited.
[0272] The display device DD includes the input sensing layer ISL on the display panel DP and the color filter layer CFL on the input sensing layer ISL.
[0273] The input sensing layer ISL may be directly on the encapsulation layer TFE. The input sensing layer ISL includes a first conductive layer ICL**1**, an insulating layer IL, a second conductive layer ICL**2**, and a protective layer PL. The first conductive layer ICL**1** may be on the encapsulation layer TFE. Although FIGS. **12**A and **12**B illustrate the structure in which the first conductive layer ICL**1** is directly on the encapsulation layer TFE, the present disclosure is not limited thereto. The input sensing layer ISL may further include a base insulating layer between the first conductive layer ICL**1** and the encapsulation layer TFE. In this case, the encapsulation layer TFE may be covered by the base insulating layer, and the first conductive layer ICL**1** may be on the base insulating layer. In an embodiment of the present disclosure, the base insulating layer may include an inorganic insulating material.

[0274] The insulating layer IL may cover the first conductive layer ICL**1**. The second conductive layer ICL**2** is on the insulating layer IL. Although FIGS. **12**A and **12**B illustrate a structure in which the input sensing layer ISL includes the first and second conductive layers ICL**1** and ICL**2**, the present disclosure is not limited thereto. For example, the input sensing layer ISL may include only one of the first and second conductive layers ICL**1** and ICL**2**.
[0275] The protective layer PL may be on the second conductive layer ICL**2**. The protective layer PL may include an organic insulating material. The protective layer PL may serve to protect the first and second conductive layers ICL**1** and ICL**2** from moisture/oxygen and may serve to protect the first and second conductive layers ICL**1** and ICL**2** from foreign matter.
[0276] The color filter layer CFL may be on the input sensing layer ISL. The color filter layer CFL may be directly on the protective layer PL. The color filter layer CFL may include a first color filter CF_R, a second color filter CF_G, and a third color filter CF_B. The first color filter CF_R has the first color, the second color filter CF_G has the second color, and the third color filter CF_B has the third color. In an embodiment of the present disclosure, the first color may be red, the second color may be green, and the third color may be blue.
[0277] The color filter layer CFL may further include a dummy color filter DCF. In an embodiment of the present disclosure, when the area where the photoelectric conversion layer O_RL is disposed is defined as a sensing area SA and the area around the sensing area SA is defined as a non-sensing area NSA, the area of the dummy color filter DCF may correspond to the sensing area SA. The dummy color filter DCF may overlap the sensing area SA and the non-sensing area NSA. In an embodiment of the present disclosure, the dummy color filter DCF may have the same color as one of the first to third color filters CF_R, CF_G, and CF_B. In an embodiment of the present disclosure, the dummy color filter DCF may have the same green color as the second color filter CF_G.
[0278] The color filter layer CFL may further include a black matrix BM. The black matrix BM may overlap the non-pixel area NPA. The black matrix BM may overlap the first and second conductive layers ICL**1** and ICL**2** in the non-pixel area NPA. In an embodiment of the present disclosure, the black matrix BM may overlap the non-pixel area NPA and the first to third non-emissive areas NPXA-R, NPXA-B, and NPXA-B. The black matrix BM may not overlap the first to third emissive areas PXA-R, PXA-G, and PXA-B.
[0279] The color filter layer CFL may further include an overcoating layer OCL. The overcoating layer OCL may include an organic insulating material. The overcoating layer OCL may have a thickness sufficient to remove steps between the first to third color filters CF_R, CF_G, and CF_B. Without any specific limitation, the overcoating layer OCL may include any material that has a certain thickness and is capable of flattening the upper surface of the color filter layer CFL. For example, the overcoating layer OCL may include an acrylic organic material.
[0280] Referring to FIG. **12**B, when the display device DD (refer to FIG. **1**) operates, the red, green, and blue light emitting elements ED_R, ED_G, and ED_B may output light. The red light emitting elements ED_R output red light in a red wavelength band, the green light emitting elements ED_G output green light in a green wavelength band, and the blue light emitting elements ED_B output blue light in a blue wavelength band.
[0281] In an embodiment of the present disclosure, the light receiving element OPD may receive light from specific light emitting elements (e.g., the green light emitting elements ED_G) among the red, green, and blue light emitting elements ED_R, ED_G, and ED_B. That is, second light Lg**1** may be output from the green light emitting elements ED_G, and the light receiving element OPD may receive second reflected light Lg**2** obtained by reflection of the second light Lg**1** from the user's fingerprint. The second light Lg**1** and the second reflected light Lg**2** may be green light in the green wavelength band. The dummy color filter DCF is disposed over the light receiving element OPD. The dummy color filter DCF may be green in color. Accordingly, the second reflected light Lg**2** may pass through the dummy color filter DCF and may be incident to the light receiving

element OPD.
[0282] The red light output from the red light emitting elements ED_R and the blue light output from the blue light emitting elements ED_B may also be reflected by the user's hand US_F. For example, when light obtained by reflection of red light Lr**1** output from the red light emitting elements ED_R by the user's hand US_F is defined as first reflected light Lr**2**, the first reflected light Lr**2** may fail to pass through the dummy color filter DCF and may be absorbed by the dummy color filer DCF. Accordingly, the first reflected light Lr**2** is not able to pass through the dummy color filter DCF and is not incident on the light receiving element OPD. Likewise, even though blue light is reflected by the user's hand US_F, the blue light may be absorbed by the dummy color filter DCF. Thus, only the second reflected light Lg**2** may be provided to the light receiving element OPD.
[0283] As described above, the readout lines may be divided into the first and second readout lines, and the second readout lines may be connected with the sensor IC through the connecting lines. Portions of the connecting lines may be disposed in the display area, and thus the area of the region occupied by the connecting lines in the non-display area may be decreased. Accordingly, the area of dead space of the display panel may be decreased.
[0284] In addition, a shielding pattern having a constant potential may be disposed between the connecting lines and the gate wirings, and the shielding pattern may decrease the coupling capacitance formed between the connecting lines and the gate wirings. Thus, a deviation in coupling capacitance between the first and second readout lines may be decreased. Accordingly, deterioration in the sensing accuracy of the sensor due to a deviation in coupling capacitance may be prevented.
[0285] While the present disclosure has been described with reference to embodiments thereof, it will be apparent to those of ordinary skill in the art that various changes and modifications may be made thereto without departing from the spirit and scope of the present disclosure as set forth in the following claims.

Claims

1. A display device having a display area and a non-display area, the display device comprising: a base layer; a circuit layer on the base layer; and an element layer on the circuit layer, the element layer including light emitting elements and light receiving elements in the display area, wherein the circuit layer includes: pixel driving circuits connected to the light emitting elements; sensor driving circuits connected to the light receiving elements; data lines connected to the pixel driving circuits; gate wirings connected to the pixel driving circuits; first readout lines connected to a first group of sensor driving circuits among the sensor driving circuits; second readout lines spaced apart from the first readout lines in a first direction and connected to a second group of sensor driving circuits among the sensor driving circuits; connecting lines electrically connected with the second readout lines, respectively, in the display area; and a shielding pattern configured to overlap the gate wirings and the connecting lines when viewed from above a plane and disposed between the gate wirings and the connecting lines in a normal direction perpendicular to the plane.
2. The display device of claim 1, wherein the connecting lines include: a plurality of vertical connecting lines extending along the first readout lines; and a plurality of horizontal connecting lines extending in the first direction and electrically connect the plurality of vertical connecting lines to the second readout lines, and wherein the shielding pattern overlaps the plurality of vertical connecting lines when viewed from above the plane.
3. The display device of claim 2, wherein the shielding pattern is over the gate wirings and under the plurality of vertical connecting lines.
4. The display device of claim 3, wherein the horizontal connecting lines are disposed on a layer different from a layer on which the vertical connecting lines are disposed, and wherein the

shielding pattern is disposed on a layer different from the layer on which the vertical connecting lines are disposed.

5. The display device of claim 2, wherein the circuit layer further includes a plurality of voltage lines connected to the pixel driving circuits, and wherein the shielding pattern is connected to at least one of the voltage lines and has a constant potential.

6. The display device of claim 5, wherein the plurality of voltage lines include: a first initialization voltage line configured to apply a first initialization voltage to the pixel driving circuits; and a second initialization voltage line configured to apply a second initialization voltage to the pixel driving circuits, and wherein the shielding pattern includes a first shielding pattern electrically connected to the second initialization voltage line.

7. The display device of claim 6, wherein the second initialization voltage line includes: a second horizontal initialization voltage line configured to extend in the first direction; and a second vertical initialization voltage line configured to extend in a second direction crossing the first direction and disposed on a layer different from a layer on which the second horizontal initialization voltage line is disposed.

8. The display device of claim 7, wherein the vertical connecting lines are on the same layer as the second vertical initialization voltage line, and wherein the first shielding pattern extends from the second horizontal initialization voltage line.

9. The display device of claim 8, wherein the gate wirings include: a first gate wiring configured to supply a black scan signal to a corresponding pixel driving circuit; a second gate wiring configured to supply an emission control signal to the corresponding pixel driving circuit; a third gate wiring configured to supply a write scan signal to the corresponding pixel driving circuit; and a fourth gate wiring configured to supply a compensation scan signal to the corresponding pixel driving circuit, and wherein the first shielding pattern overlaps the first and second gate wirings when viewed from above the plane.

10. The display device of claim 6, wherein the shielding pattern further includes a second shielding pattern connected to the first initialization voltage line.

11. The display device of claim 10, wherein the first initialization voltage line includes: a first horizontal initialization voltage line configured to extend in the first direction; and a first vertical initialization voltage line configured to extend in a second direction crossing the first direction and disposed on a layer different from a layer on which the first horizontal initialization voltage line is disposed.

12. The display device of claim 11, wherein the vertical connecting lines are on the same layer as the first vertical initialization voltage line, and wherein the second shielding pattern extends from the first horizontal initialization voltage line.

13. The display device of claim 12, wherein the gate wirings include: a first gate wiring configured to supply a black scan signal to a corresponding pixel driving circuit; a second gate wiring configured to supply an emission control signal to the corresponding pixel driving circuit; a third gate wiring configured to supply a write scan signal to the corresponding pixel driving circuit; and a fourth gate wiring configured to supply a compensation scan signal to the corresponding pixel driving circuit, and wherein the second shielding pattern overlaps the third and fourth gate wirings when viewed from above the plane.

14. The display device of claim 1, wherein the data lines include: first data lines connected to a first group of pixel driving circuits among the pixel driving circuits; and second data lines spaced apart from the first data lines in the first direction and connected to a second group of pixel driving circuits among the pixel driving circuits, and wherein the circuit layer further includes data connecting lines electrically connected with the second data lines, respectively, in the display area.

15. The display device of claim 1, further comprising: a driver chip electrically connected to the circuit layer; and a sensor chip electrically connected to the circuit layer, wherein the second readout lines are connected to the sensor chip through the connecting lines.

16. The display device of claim 15, wherein the driver chip and the sensor chip are adjacent to one side of the display area.

17. An electronic device having a display area and a non-display area, the electronic device comprising: a base layer; a circuit layer on the base layer; and an element layer on the circuit layer, the element layer including light emitting elements and light receiving elements in the display area, wherein the circuit layer includes: pixel driving circuits connected to the light emitting elements; sensor driving circuits connected to the light receiving elements; data lines connected to the pixel driving circuits; gate wirings connected to the pixel driving circuits; voltage lines connected to the pixel driving circuits; first readout lines connected to a first group of sensor driving circuits among the sensor driving circuits; second readout lines spaced apart from the first readout lines in a first direction and connected to a second group of sensor driving circuits among the sensor driving circuits; vertical connecting lines electrically connected with the second readout lines, respectively, in the display area and configured to cross the gate wirings; and a shielding pattern configured to overlap the gate wirings and the vertical connecting lines when viewed from above a plane and disposed between the gate wirings and the vertical connecting lines in a normal direction perpendicular to the plane, wherein the shielding pattern extends from at least one of the voltage lines.

18. The electronic device of claim 17, wherein the voltage lines include: a first initialization voltage line configured to apply a first initialization voltage to the pixel driving circuits; and a second initialization voltage line configured to apply a second initialization voltage to the pixel driving circuits, and wherein the shielding pattern includes a first shielding pattern electrically connected to the second initialization voltage line.

19. The electronic device of claim 18, wherein the second initialization voltage line includes: a second horizontal initialization voltage line extending in the first direction; and a second vertical initialization voltage line extending in a second direction crossing the first direction and disposed on a layer different from a layer on which the second horizontal initialization voltage line is disposed.

20. The electronic device of claim 19, wherein the vertical connecting lines are on the same layer as the second vertical initialization voltage line, and wherein the first shielding pattern extends from the second horizontal initialization voltage line.

21. The electronic device of claim 20, wherein the gate wirings include: a first gate wiring configured to supply a black scan signal to a corresponding pixel driving circuit; a second gate wiring configured to supply an emission control signal to the corresponding pixel driving circuit; a third gate wiring configured to supply a write scan signal to the corresponding pixel driving circuit; and a fourth gate wiring configured to supply a compensation scan signal to the corresponding pixel driving circuit, and wherein the first shielding pattern overlaps the first and second gate wirings when viewed from above the plane.

22. The electronic device of claim 18, wherein the shielding pattern further includes a second shielding pattern connected to the first initialization voltage line.

23. The electronic device of claim 22, wherein the first initialization voltage line includes: a first horizontal initialization voltage line extending in the first direction; and a first vertical initialization voltage line extending in a second direction crossing the first direction and disposed on a layer different from a layer on which the first horizontal initialization voltage line is disposed.

24. The electronic device of claim 23, wherein the vertical connecting lines are on the same layer as the first vertical initialization voltage line, and wherein the second shielding pattern extends from the first horizontal initialization voltage line.

25. The electronic device of claim 24, wherein the gate wirings include: a first gate wiring configured to supply a black scan signal to a corresponding pixel driving circuit; a second gate wiring configured to supply an emission control signal to the corresponding pixel driving circuit; a third gate wiring configured to supply a write scan signal to the corresponding pixel driving circuit;

and a fourth gate wiring configured to supply a compensation scan signal to the corresponding pixel driving circuit, and wherein the second shielding pattern overlaps the third and fourth gate wirings when viewed from above the plane.

26. The electronic device of claim 17, further comprising: a driver chip electrically connected to the circuit layer; and a sensor chip electrically connected to the circuit layer, wherein the second readout lines are connected to the sensor chip through the vertical connecting lines.

27. The electronic device of claim 26, wherein the driver chip and the sensor chip are disposed adjacent to one side of the display area.